

Load Disconnection Function, 0.8A Step-up DC/DC Converters

GreenOperation-compatible

GENERAL DESCRIPTION

XC9141/XC9142 series are synchronous step-up DC/DC converters with a 0.3Ω (TYP.) N-channel driver transistor and a 0.3Ω (TYP.) synchronous P-channel switching transistor built-in. A highly efficient and stable current can be supplied up to 0.8A by reducing ON resistance of the built-in transistors.

The series are able to start operation under the condition which has 0.9V input voltage to generate 3.3V output voltage with a 100 Ω load resistor, suitable for mobile equipment using only one Alkaline battery or one Nickel metal hydride battery.

The output voltage can be set from 1.8V to 5.5V ($\pm 2.0\%$) in steps of 0.1V. With the built-in oscillator, either 1.2MHz or 3.0MHz can be selected for suiting to your particular application.

During the devices enter stand-by mode, A, D types prevent the application malfunction by C_L Discharge Function which can quickly discharge the electric charge at the output capacitor (C_L). B, E types is able to drive RTC etc. by Bypass Switch Function to maintain continuity between the input and output. C, F types is able to connect in parallel with other power supplies by Load Disconnection Function which breaks continuity between the input and output. * D, E, and F types are under development.

APPLICATIONS

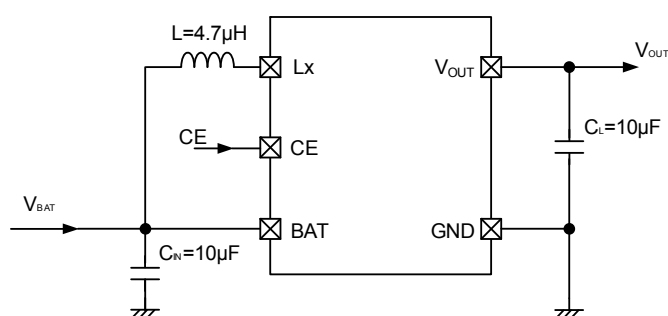
Portable equipment
Beauty & health equipment
Wearable devices
Game & Hobby
PC Peripherals
Devices with 1~3 Alkaline,
1~3 Nickel Hydride, 1 Lithium and 1 Li-ion

FEATURES

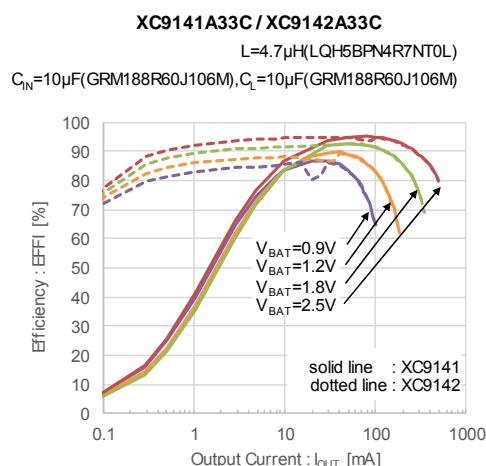
Input Voltage Range	: 0.65V ~ 6.0V
Fixed Output Voltage	: 1.8V ~ 5.5V (0.1V increments)
Oscillation Frequency	: 1.2MHz ($\pm 15\%$), 3.0MHz ($\pm 20\%$)
Input Current	: 0.8A
Output Current	: 500mA @ $V_{OUT}=5.0V$, $V_{BAT}=3.3V$ (TYP.) 350mA @ $V_{OUT}=3.3V$, $V_{BAT}=1.8V$ (TYP.)
Control Mode Selection	: PWM (XC9141 Series) or Auto PWM/PFM (XC9142 Series)
Load Transient Response	: 100mV @ $V_{OUT}=3.3V$, $V_{BAT}=1.8V$, $I_{OUT}=1mA \rightarrow 200mA$
Protection Circuits	: Over-current limit Integral latch method (D,E,F type) Output short-circuit protection (D,E,F type)
Functions	: Soft-start Load Disconnection Function (A,C,D,F type) C_L Auto Discharge Function (A,D type) Bypass Switch Function (B,E type)
Output Capacitor	: Ceramic Capacitor
Operating Ambient Temperature	: -40 ~ +85
Package	: SOT-25, USP-6C, WLP-6-01
Environmentally Friendly	: EU RoHS Compliant, Pb Free

* D, E, and F types are under development.

TYPICAL APPLICATION CIRCUIT



TYPICAL PERFORMANCE CHARACTERISTICS



PRODUCT CLASSIFICATION

Ordering Information

XC9141 - PWM control

DESIGNATOR	ITEM	SYMBOL	DESCRIPTION
	Type	A	Refer to Selection Guide
		B	
		D ^(*)	
		E ^(*)	
	Output Voltage	18 ~ 55	Output voltage options e.g. 1.8V → =1, =8
	Oscillation Frequency	C	1.2MHz
		D	3.0MHz
- ^(*)	Packages (Order Unit)	MR-G	SOT-25 (3,000pcs/Reel)
		ER-G	USP-6C (3,000pcs/Reel)
		0R-G	WLP-6-01 (5,000pcs/Reel)

^(*) The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully EU RoHS compliant.

^(*) D and E types are under development.

XC9142 - PWM/PFM automatic switching control

DESIGNATOR	ITEM	SYMBOL	DESCRIPTION
	Type	A	Refer to Selection Guide
		B	
		C	
		D ^(*)	
		E ^(*)	
		F ^(*)	
	Output Voltage	18 ~ 55	Output voltage options e.g. 1.8V → =1, =8
	Oscillation Frequency	C	1.2MHz
		D	3.0MHz
- ^(*)	Packages (Order Unit)	MR-G	SOT-25 (3,000pcs/Reel)
		ER-G	USP-6C (3,000pcs/Reel)
		0R-G	WLP-6-01 (5,000pcs/Reel)

^(*) The "-G" suffix indicates that the products are Halogen and Antimony free as well as being fully EU RoHS compliant.

^(*) D, E, and F types are under development.

Selection guides

TYPE	OUTPUT VOLTAGE	CHIP ENABLE	SOFT-START	CURRENT LIMIT	SHORT PROTECTION WITH LATCH	C _L AUTO-DISCHARGE	SHUTDOWN OPTIONS AT CE=L
A	Fixed	Yes	Fixed	Yes (without latch)	No	Yes	Complete Output Disconnect ^(*)
B	Fixed	Yes	Fixed	Yes (without latch)	No	No	Input-to-Output Bypass ^(*)
C ^(*)	Fixed	Yes	Fixed	Yes (without latch)	No	No	Complete Output Disconnect ^(*)
D ^(*)	Fixed	Yes	Fixed	Yes (with integral latch)	Yes	Yes	Complete Output Disconnect ^(*)
E ^(*)	Fixed	Yes	Fixed	Yes (with integral latch)	Yes	No	Input-to-Output Bypass ^(*)
F ^(*) ^(*)	Fixed	Yes	Fixed	Yes (with integral latch)	Yes	No	Complete Output Disconnect ^(*)

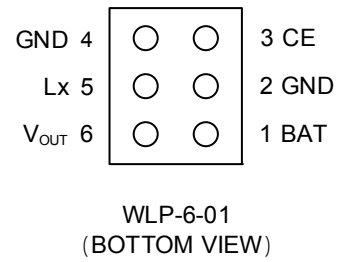
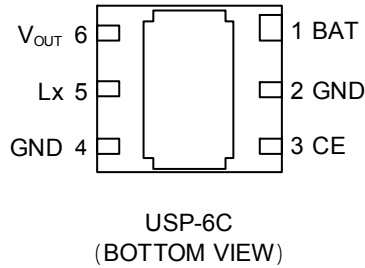
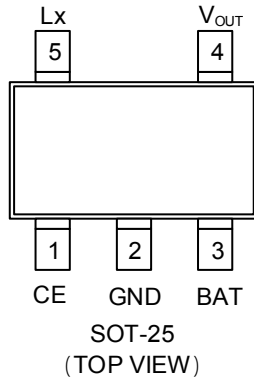
^(*) Type C,F is available for the XC9142 series only.

^(*) V_{OUT} pin can not be connected to the different output pin such as another supply (AC adaptor).

^(*) V_{OUT} pin can be connected to the different output pin such as another supply (AC adaptor).

^(*) D, E, and F types are under development.

PIN CONFIGURATION



*The dissipation pad for the USP-6C package should be solder-plated in recommended mount pattern and metal masking so as to enhance mounting strength and heat release. If the pad needs to be connected to other pins, it should be connected to the GND (No.2, 4) pin.

PIN ASSIGNMENT

PIN NUMBER			PIN NAME	FUNCTIONS
SOT-25	USP-6C	WLP-6-01		
1	3	3	CE	Chip Enable
2	2	2	GND	Ground
3	1	1	BAT	Power Input
4	6	6	V _{OUT}	Output Voltage
5	5	5	Lx	Switching
-	4	4	GND	Ground

FUNCTION CHART

PIN NAME	SIGNAL	STATUS
CE	L	Stand-by
	H	Active

* Do not leave the CE pin open.

ABSOLUTE MAXIMUM RATINGS

T_a=25

PARAMETER		SYMBOL	RATINGS	UNITS
BAT Pin Voltage		V _{BAT}	-0.3 ~ +7.0	V
Lx Pin Voltage		V _{Lx}	-0.3 ~ +7.0	V
V _{OUT} Pin Voltage		V _{OUT}	-0.3 ~ +7.0	V
CE Pin Voltage		V _{CE}	-0.3 ~ +7.0	V
Power Dissipation	SOT-25	Pd	600 (PCB mounted)	mW
	USP-6C		1000 (PCB mounted)	
	WLP-6-01		700 (PCB mounted)	
Operating Ambient Temperature		T _{opr}	-40 ~ +85	
Storage Temperature		T _{stg}	-55 ~ +125	

*GND are standard voltage for all of the voltage.

ELECTRICAL CHARACTERISTICS

XC9141/XC9142 Series

Ta=25

PARAMETER	SYMBOL	CONDITIONS		MIN.	TYP.	MAX.	UNITS	CIRCUIT
Input Voltage	V_{BAT}			-	-	6.0	V	
Output Voltage	V_{OUT}	Voltage to start oscillation while $V_{OUT}=V_{OUT(T)} \times 1.03 \rightarrow V_{OUT(T)} \times 0.97$		<E-1>	<E-2>	<E-3>	V	
Operation Start Voltage	V_{ST1}	$R_L=1k\Omega$		-	-	0.90	V	
Operation Hold Voltage	V_{HLD}	$R_L=1k\Omega$		-	0.65	-	V	
Quiescent Current (XC9142)	I_q	$V_{OUT}=V_{BAT}=V_{OUT(T)}+0.5V$	$f_{OSC}=1.2MHz$	-	17.0	30.0	μA	
			$f_{OSC}=3.0MHz$	-	26.0	40.0		
Supply Current	I_{DD}	$V_{OUT}=V_{BAT}=V_{OUT(T)}-0.2V$	$f_{OSC}=1.2MHz$	-	<E-4>	1.500	mA	
			$f_{OSC}=3.0MHz$	-	<E-5>	3.000		
Oscillation Frequency	f_{OSC}	$V_{BAT}=V_{OUT(T)} \times 0.5$ $I_{OUT}=100mA$	$f_{OSC}=1.2MHz$	1.02	1.20	1.38	MHz	
			$f_{OSC}=3.0MHz$	2.40	3.00	3.60		
Maximum Duty Cycle	D_{MAX}	$V_{BAT}=1.2V$, $V_{OUT}=V_{OUT(T)}-0.2V$	$f_{OSC}=1.2MHz$	85	93	98	%	
			$f_{OSC}=3.0MHz$	88	93	98		
Minimum Duty Cycle	D_{MIN}	$V_{OUT}=V_{BAT}=V_{OUT(T)}+0.5V$		-	-	0	%	
PFM Switching Current	I_{PFM}	$V_{BAT}=1.5V$, R_L is selected with $V_{OUT(T)}$, Refer to Table 1.		-	165	230	mA	
Efficiency (XC9142)	EFFI	$V_{BAT}=V_{OUT(T)} \times 0.6$, R_L is selected with $V_{OUT(T)}$, Refer to Table 1.		-	86 ^{(*)3}	-	%	
Efficiency	EFFI	$V_{BAT}=V_{OUT(T)} \times 0.6$, $I_{OUT}=100mA$		-	90 ^{(*)3}	-		
Stand-by Current	I_{STB}	$V_{BAT}=V_{Lx}=6.0V, V_{CE}=0.0V^{(*)1}$	A,B Type	-	0.0	1.0	μA	
			C Type	-	1.0	2.4		
Lx SW "Pch" ON Resistance	R_{LXP}	$V_{BAT}=V_{Lx}=6.0V, I_{OUT}=200mA$		-	0.3 ^{(*)2}	-	Ω	
Lx SW "Nch" ON Resistance	R_{LXN}			-	0.3 ^{(*)3}	-	Ω	
Lx SW "H" Leakage Current	I_{LXLH}	$V_{BAT}=6.0V, V_{CE}=0.0V$, $V_{Lx}=6.0V^{(*)1}$	A,B Type	-	0.0	1.0	μA	
			C Type	-	0.0	1.0		
Lx SW "L" Leakage Current (XC9142C)	I_{LXLL}	$V_{BAT}=0.0V, V_{CE}=0.0V, V_{Lx}=0.0V, V_{OUT}=6.0V$		-	0.0	1.0	μA	
Current Limit	I_{LIM}	$V_{BAT}=V_{OUT(T)}-0.2V, R_{Lx}=1\Omega$		<E-6>	<E-7>	<E-8>	A	

ELECTRICAL CHARACTERISTICS (Continued)

PARAMETER	SYMBOL	CONDITIONS		MIN.	TYP.	MAX.	UNITS	CIRCUIT
Soft-Start Time	t _{SS}	V _{BAT} = V _{OUT(T)} ×0.6, V _{OUT} =V _{OUT(T)} × 0.9, After "H" is fed to CE, the time by when clocks are generated at Lx pin.	f _{OSC} =1.2MHz	0.6	1.0	2.5	ms	
			f _{OSC} =3.0MHz	0.2	0.5	1.0		
C _L Discharge Resistance (A Type)	R _{DCHG}	V _{BAT} = 3.3V,V _{OUT} =3.3V,V _{CE} =0.0V		100	180	400	Ω	
Bypass SW Resistance (B Type)	R _{BSW}	V _{BAT} = 3.3V,V _{OUT} =0.0V,V _{CE} =0.0V		100	180	400	Ω	
CE "H" Voltage	V _{CEH}	V _{OUT} = V _{OUT(T)} -0.15V, Applied voltage to V _{CE} , Voltage changes Lx to be generated.		0.80	-	6.00	V	
CE "L" Voltage	V _{CEL}	V _{OUT} = V _{OUT(T)} -0.15V, Applied voltage to V _{CE} , Voltage changes Lx to"H" level.		GND	-	0.20	V	
CE "H" Current	I _{CEH}	V _{BAT} =6.0V,V _{OUT} =6.0V, V _{Lx} =6.0V, V _{CE} =6.0V		-0.1	-	0.1	μA	
CE "L" Current	I _{CEL}	V _{BAT} =6.0V,V _{OUT} =6.0V, V _{Lx} =6.0V, V _{CE} =0.0V		-0.1	-	0.1	μA	

$V_{OUT(T)}$ = Target voltage

Test Conditions: unless otherwise stated, $V_{BAT} = 1.5\text{V}$, $V_{ce} = 3.3\text{V}$, Lx: OPEN, $R_{Lx} = 56\Omega$

(*1) XC9141A/XC9142A/XC9142C type: $V_{OUT} = 0\text{V}$,

XC9141B/XC9142B type: $V_{OUT} = \text{OPEN}$

(*2) Design value for the XC9142C type.

(*3) Designed value

Table 1. External Components R_L Table

$V_{OUT(T)}$	R_L
UNITS: V	UNITS: Ω
1.8 $V_{OUT(T)} < 2.1$	150
2.1 $V_{OUT(T)} < 3.1$	220
3.1 $V_{OUT(T)} < 4.3$	330
4.3 $V_{OUT(T)} \leq 5.5$	470

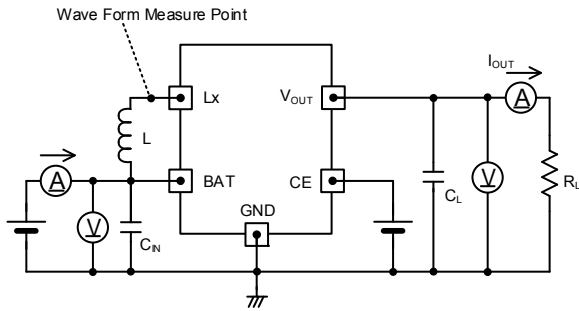
ELECTRICAL CHARACTERISTICS (Continued)

Table 2: SPEC Table

NOMINAL OUTPUT VOLTAGE	V _{OUT}			I _{DD}		I _{LIM}		
				f _{osc} =1.2MHz	f _{osc} =3.0MHz			
	<E-1>	<E-2>	<E-3>	<E-4>	<E-5>	<E-6>	<E-7>	<E-8>
UNITS	V	V	V	mA	mA	A	A	A
V _{OUT(T)}	MIN.	TYP.	MAX.	TYP.	TYP.	MIN.	TYP.	MAX.
1.8	1.764	1.800	1.836	0.263	0.583	-	0.96	2.30
1.9	1.862	1.900	1.938	0.279	0.614	-	1.00	2.30
2.0	1.960	2.000	2.040	0.296	0.644	-	1.04	2.30
2.1	2.058	2.100	2.142	0.312	0.675	-	1.07	2.30
2.2	2.156	2.200	2.244	0.328	0.705	-	1.11	2.30
2.3	2.254	2.300	2.346	0.344	0.736	-	1.14	2.30
2.4	2.352	2.400	2.448	0.360	0.767	-	1.17	2.30
2.5	2.450	2.500	2.550	0.376	0.797	-	1.19	2.30
2.6	2.548	2.600	2.652	0.393	0.828	-	1.22	2.30
2.7	2.646	2.700	2.754	0.409	0.858	-	1.24	2.30
2.8	2.744	2.800	2.856	0.425	0.889	-	1.26	2.30
2.9	2.842	2.900	2.958	0.441	0.919	-	1.28	2.30
3.0	2.940	3.000	3.060	0.457	0.950	0.96	1.30	2.30
3.1	3.038	3.100	3.162	0.474	0.981	0.97	1.30	2.30
3.2	3.136	3.200	3.264	0.490	1.011	0.97	1.30	2.30
3.3	3.234	3.300	3.366	0.506	1.042	0.98	1.30	2.30
3.4	3.332	3.400	3.468	0.522	1.072	0.98	1.30	2.30
3.5	3.430	3.500	3.570	0.538	1.103	0.99	1.30	2.30
3.6	3.528	3.600	3.672	0.554	1.134	0.99	1.30	2.30
3.7	3.626	3.700	3.774	0.571	1.164	1.00	1.30	2.30
3.8	3.724	3.800	3.876	0.587	1.195	1.00	1.30	2.30
3.9	3.822	3.900	3.978	0.603	1.225	1.01	1.30	2.30
4.0	3.920	4.000	4.080	0.619	1.256	1.01	1.30	2.30
4.1	4.018	4.100	4.182	0.635	1.286	1.02	1.30	2.30
4.2	4.116	4.200	4.284	0.652	1.317	1.02	1.30	2.30
4.3	4.214	4.300	4.386	0.668	1.348	1.03	1.30	2.30
4.4	4.312	4.400	4.488	0.684	1.378	1.03	1.30	2.30
4.5	4.410	4.500	4.590	0.700	1.409	1.04	1.30	2.30
4.6	4.508	4.600	4.692	0.716	1.439	1.04	1.30	2.30
4.7	4.606	4.700	4.794	0.732	1.470	1.05	1.30	2.30
4.8	4.704	4.800	4.896	0.749	1.501	1.06	1.30	2.30
4.9	4.802	4.900	4.998	0.765	1.531	1.06	1.30	2.30
5.0	4.900	5.000	5.100	0.781	1.562	1.07	1.30	2.30
5.1	4.998	5.100	5.202	0.797	1.592	1.07	1.30	2.30
5.2	5.096	5.200	5.304	0.813	1.623	1.08	1.30	2.30
5.3	5.194	5.300	5.406	0.829	1.653	1.08	1.30	2.30
5.4	5.292	5.400	5.508	0.846	1.684	1.09	1.30	2.30
5.5	5.390	5.500	5.610	0.862	1.715	1.09	1.30	2.30

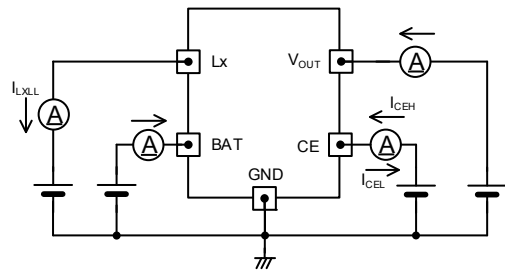
TEST CIRCUITS

< Circuit No. >

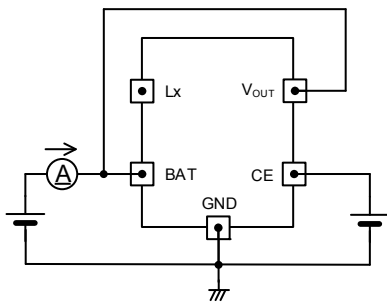


External Components
 C_N : 10 μ F (ceramic)
 C_L : 10 μ F (ceramic)
 XC914xxxxC ($f_{OSC} = 1.2$ MHz)
 L : 4.7 μ H
 XC914xxxxD ($f_{OSC} = 3.0$ MHz)
 L : 2.2 μ H

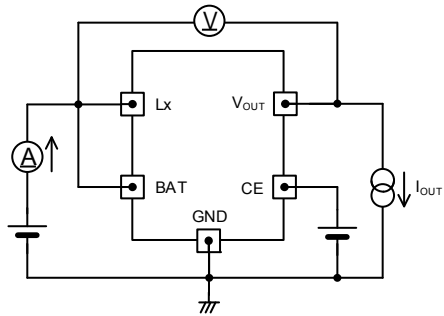
< Circuit No. >



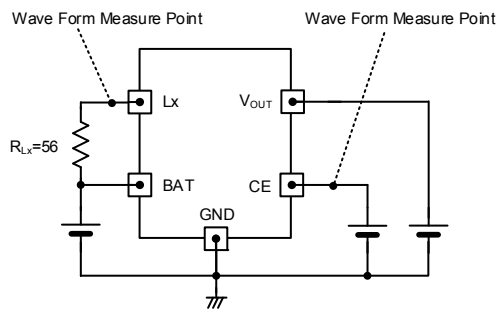
< Circuit No. >



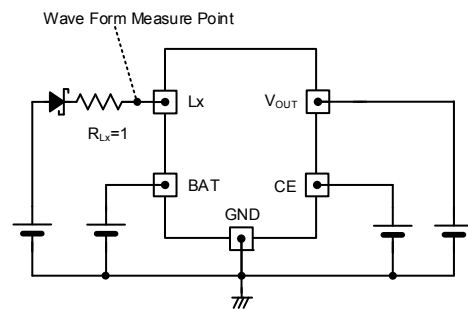
< Circuit No. >



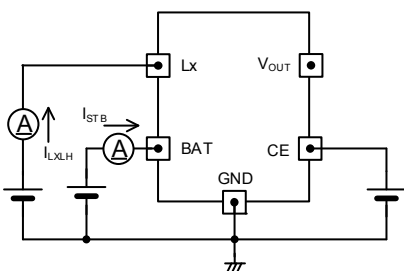
< Circuit No. >



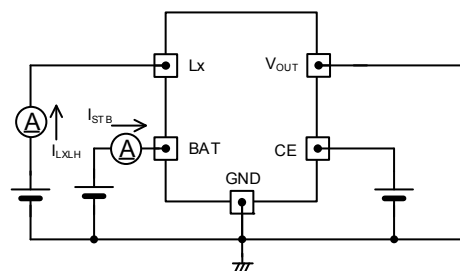
< Circuit No. >



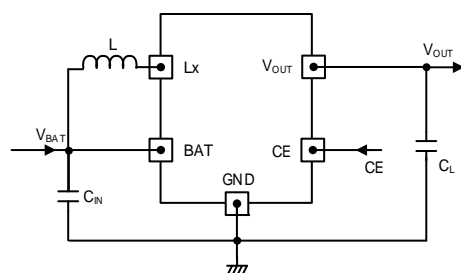
< Circuit No. >



< Circuit No. >



TYPICAL APPLICATION CIRCUIT



【Typical Examples】 $f_{osc}=1.2\text{MHz}$

	MANUFACTURER	PRODUCT NUMBER	VALUE
L	murata	LQH5BPN4R7NT0L	4.7 μH
	TDK	LTF5022T-4R7N2R0-LC	4.7 μH
	Coilcraft	XFL4020-472MEC	4.7 μH
$C_L^{(*)1}$	murata	GRM188R60J106ME84	10 $\mu\text{F}/6.3\text{V}^{(*)2}$
	murata	GRM188D71A106MA73	10 $\mu\text{F}/10\text{V}^{(*)2}$

【Typical Examples】 $f_{osc}=3.0\text{MHz}$

	MANUFACTURER	PRODUCT NUMBER	VALUE
L	TDK	LTF5022T-2R2N3R2-LC	2.2 μH
	Coilcraft	XFL4020-222MEC	2.2 μH
$C_L^{(*)1}$	murata	GRM188R60J106ME84	10 $\mu\text{F}/6.3\text{V}^{(*)2}$
	murata	GRM188D71A106MA73	10 $\mu\text{F}/10\text{V}^{(*)2}$

【Typical Examples】 $f_{osc}=1.2\text{MHz}$, $f_{osc}=3.0\text{MHz}$

	MANUFACTURER	PRODUCT NUMBER	VALUE
$C_{IN}^{(*)1}$	murata	GRM188R60J106ME84	10 $\mu\text{F}/6.3\text{V}$
	murata	GRM188D71A106MA73	10 $\mu\text{F}/10\text{V}$

(^{*)1}) Select components appropriate to the usage conditions (ambient temperature, input & output voltage).

While selecting a part, please concern about capacitance reduction and voltage durability.

(^{*)2}) In the case of $f_{osc}=1.2\text{MHz}$: If $V_{OUT(T)} \leq 3.5\text{V}$ and the load current rises above 200mA, use two or more in a parallel connection.

In the case of $f_{osc}=3.0\text{MHz}$: If $V_{BAT} \leq 2\text{V}$, $V_{OUT(T)} \leq 3.5\text{V}$ and the load current rises above 200mA, use two or more in a parallel connection.

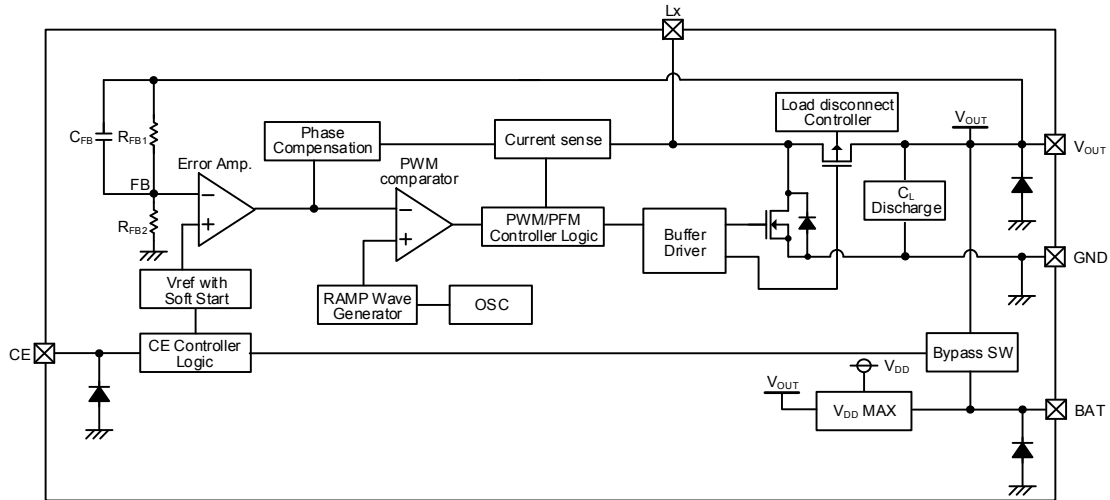
For the actual load capacitance, use a ceramic capacitor that ensures a capacitance equivalent to or greater than the GRM188R60J106ME84 (Murata).

If using tantalum or low ESR electrolytic capacitors please be aware that ripple voltage will be higher due to the larger ESR (Equivalent Series Resistance) values of those types of capacitors. Please also note that the IC's operation may become unstable with such capacitors so that we recommend to test on the board before usage.

If using electrolytic capacitor for the C_L , please connect a ceramic capacitor in parallel.

OPERATIONAL EXPLANATION

The XC9141/XC9142 series consists of a reference voltage source, ramp wave circuit, error amplifier, PWM comparator, phase compensation circuit, N-channel driver transistor, P-channel synchronous rectification switching transistor and current limiter circuit.



BLOCK DIAGRAM

The error amplifier compares the internal reference voltage with the resistors RFB1 and RFB2. Phase compensation is performed on the resulting error amplifier output, to input a signal to the PWM comparator to determine the turn-on time of the N-channel driver transistor during PWM operation. The PWM comparator compares, in terms of voltage level, the signal from the error amplifier with the ramp wave from the ramp wave circuit, and delivers the resulting output to the buffer driver circuit to cause the Lx pin to output a switching duty cycle. This process is continuously performed to ensure stable output voltage. The current feedback circuit monitors the N-channel driver transistor's turn-on current for each switching operation, and modulates the error amplifier output signal to provide multiple feedback signals. This enables a stable feedback loop even when a low ESR capacitor, such as a ceramic capacitor, is used, ensuring stable output voltage.

<Reference voltage source, soft start function>

The reference voltage forms a reference that is used to stabilize the output voltage of the IC.

After "H" level is fed to CE pin, the reference voltage connected to the error amp increases linearly during the soft start interval. This allows the voltage divided by the internal RFB1 and RFB2 resistors and the reference voltage to be controlled in a balanced manner, and the output voltage rises in proportion to the rise in the reference voltage. This operation prevents rush input current and enables the output voltage to rise smoothly.

<Ramp Wave Circuit>

The ramp wave circuit determines switching frequency. The frequency is fixed internally at 1.2MHz/3.0MHz. The Clock generated is used to produce ramp waveforms needed for PWM operation, and to synchronize all the internal circuits.

<Error Amplifier>

The error amplifier is designed to monitor output voltage. The amplifier compares the reference voltage with the feedback voltage divided by the internal resistors (RFB1 and RFB2). When the FB is lower than the reference voltage, output voltage of the error amplifier increases. The gain and frequency characteristics of the error amplifier are optimized internally.

<V_{DDMAX}>

V_{DD MAX} circuit compares the input voltage and the output voltage then it will select the higher one as the power supply for the IC.

<Shutdown function, load disconnection function>

The IC enters chip disable state by applying low level voltage to the CE pin. At this time, the N-channel and P-channel synchronous switching transistors are turned OFF. With XC9142C type, the load disconnection function activates even during shutdown, and because the input voltage V_{BAT} and output voltage V_{OUT} are compared to optimally control the orientation of the parasitic diode of the P-channel synchronous switching transistor, a parallel connection with other power supplies is possible. With the XC9141 series and XC9142A/B types, the orientation of the parasitic diode of the P-channel synchronous switching transistor is fixed at anode: V_{OUT} and cathode: Lx during shutdown to break conduction from the input side to the output side by the parasitic diode of the P-channel synchronous switching transistor.

<PWM/PFM control circuit>

When PFM operates, the N-channel driver transistor turns on at the timing of the signal sent from the PWM comparator. The N-channel driver transistor remains on until the current in the coil reaches a constant current (I_{PFM}). The PWM/PFM control circuit compares the signal sent from the PWM comparator to the time it takes the current in the coil to reach a constant current (I_{PFM}), and outputs the pulse that results in a longer on-time of the N-channel driver transistor. This enables smooth switching between PWM and PFM. The XC9141 series directly outputs the signal that is sent from the PWM comparator.

OPERATIONAL EXPLANATION (Continued)

<Maximum current limit function, short-circuit protection>

The maximum current limit function of XC9141A/B types and XC9142A/B/C types constantly monitors the current flowing in the N-channel driver transistor connected to the Lx pin, and if the current in the N-channel driver transistor exceeds the current limit, the function turns off the N-channel driver transistor. (Please refer to Fig. I_{LIM})

If the current flowing in the N-channel driver transistor exceeds the current limit value (equivalent to the peak coil current), the N-channel driver transistor turns off, and remains off during the clock interval.

At the next clock, the N-channel driver transistor turns on.

If overcurrent continues, and are repeated.

Note that the current in the internal N-channel driver transistor is not the same as the output current I_{OUT} .

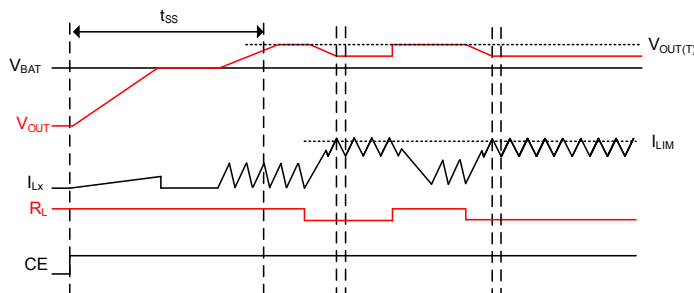


Fig. I_{LIM}

< C_L Discharge>

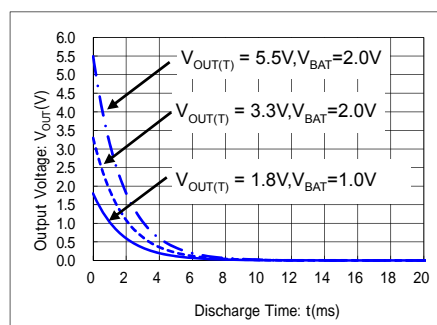
The XC9141A type and XC9142A type can discharge the electric charge at the output capacitor (C_L) when a low signal to the CE pin which enables a whole IC circuit put into OFF state, is inputted via the N-channel transistor located between the V_{OUT} pin and the GND pin. When the IC is disabled, electric charge at the output capacitor (C_L) is quickly discharged so that it may avoid application malfunction. Discharge time of the output capacitor (C_L) is set by the C_L auto-discharge resistance (R) and the output capacitor (C_L). By setting time constant of a C_L auto-discharge resistance value [R_{DCHG}] and an output capacitor value (C_L) as ($\tau = C_L \times R_{DCHG}$), discharge time of the output voltage after discharge via the N channel transistor is calculated by the following formulas. However, the C_L discharge resistance [R_{DCHG}] is depends on the V_{BAT} or V_{OUT} , so it is difficult to make sure the discharge time. We recommend that you fully check actual performance.

$$V = V_{OUT} \times e^{-t/\tau} \quad \text{or} \quad t = -\tau \times \ln(V_{OUT}/V)$$

- V : Output voltage after discharge
- $V_{OUT(T)}$: Target voltage
- t : Discharge time
- τ : $C_L \times R_{DCHG}$
- C_L : Capacitance of Output capacitor (C_L)
- R_{DCHG} : C_L Discharge resistance, it depends on supply voltage

Output Voltage Discharge characteristics

$$R_{DCHG} = 180\Omega(\text{TYP}) \quad C_L = 10\mu\text{F}$$



<Bypass switch>

At shutdown, XC9141B type and XC9142B type conduct between the BAT pin and V_{OUT} pin by means of a bypass switch. If the output is shorted to ground, the current is limited by the resistance (R_{BSW}) of the bypass switch.

NOTE ON USE

- 1) For the phenomenon of temporal and transitional voltage decrease or voltage increase, the IC may be damaged or deteriorated if IC is used beyond the absolute maximum ratings.
- 2) Spike noise and ripple voltage arise in a switching regulator as with a DC/DC converter. These are greatly influenced by external component selection, such as the coil inductance, capacitance values, and board layout of external components. Once the design has been completed, verification with actual components should be done.
- 3) The DC/DC converter performance is greatly influenced by not only the ICs' characteristics, but also by those of the external components. Care must be taken when selecting the external components. Especially for C_L load capacitor, it is recommended to use type B capacitors (JIS regulation) or X7R, X5R capacitors (EIA regulation).
- 4) Use a ground wire of sufficient strength. Ground potential fluctuation caused by the ground current during switching could cause the IC operation to become unstable, so reinforce the area around the GND pin of the IC in particular.
- 5) Please mount each external component as close to the IC as possible. Also, please make traces thick and short to reduce the circuit impedance.
- 6) With regard to the current limiting value (I_{LIM}), the actual coil current may at times exceed the electrical characteristics due to propagation delay inside the product.
- 7) The CE pin is a CMOS input pin. Do not use with the pin open. If connecting to the input or ground, use the resistor which is 1M Ω or less. To prevent malfunctioning of the device connected to this product or the input/output due to short circuiting between pins, it is recommended that a resistor be connected.
- 8) In case of connecting to another power supply as shown in below circuit diagram, please use the XC9142C type. Connecting another external power supply to the output of any other type may destroy the IC.
- 9) The maximum current limiter controls the limit of the N-channel driver transistor by monitoring current flow. This function does not limit the current flow of the P-channel synchronous transistor. When used with the condition $V_{BAT} > V_{OUT}$ (input voltage higher than the output voltage), the IC may be destroyed if overcurrent flows to the P-channel synchronous switching transistor due to short-circuiting of the load or other reason.
- 10) When the device is used in high step-up ratio, the current limit function may not work during excessive load current. In this case, the maximum duty cycle limits maximum current.
- 11) If the status heavy load and large output capacitor is connected or the input voltage is low, the output voltage may overshoot, on XC9141A/B types and XC9142A/B/C types.
- 12) When the step-up voltage difference is small, the XC9141 series for PWM control may oscillate intermittently.
- 13) When the voltage boost difference is small, the current limiting function may not operate if the on time of the N-channel driver transistor is shorter than the propagation delay time of the current limit circuit.
- 14) When an XC9142C type is used with $V_{BAT} > V_{OUT(T)}$ (input voltage higher than the set output voltage), the P-channel synchronous switching transistor turns off but current flows to the parasitic diode. This causes excessive heat generation in the IC. Test using the actual equipment and note the power dissipation and heat dissipation of the package. During voltage boosting with a voltage drop due to V_F of the parasitic diode, the output voltage may become unstable. On the XC9141 series and XC9142A/B types, the P-channel synchronous switching transistor turns on and the output voltage becomes equal to the input voltage. In environments where $V_{BAT} > V_{OUT(T)}$, the XC9141 series and XC9142A/B types are recommended.
- 15) TOREX places an importance on improving our products and its reliability. However, by any possibility, we would request user fail-safe design and post-aging treatment on system or equipment.

NOTE ON USE (Continued)

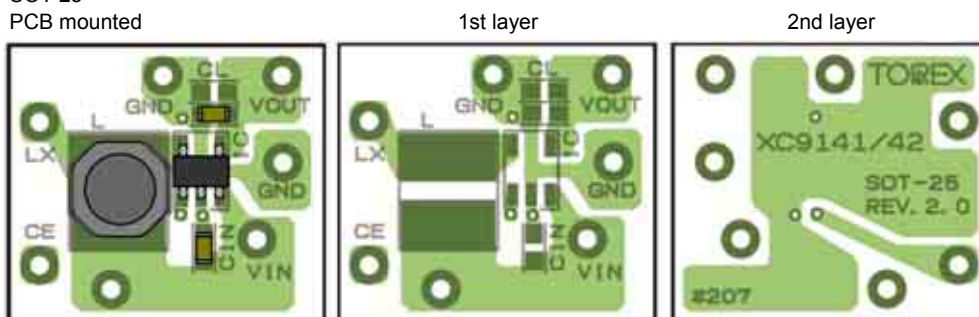
16) Instructions for pattern layouts

1. In order to stabilize V_{BAT} voltage level, we recommend that a by-pass capacitor C_{IN} is connected as close as possible to the BAT and GND pins.
2. Please mount each external component as close to the IC as possible.
3. Place external components as close to the IC as possible and use thick and short traces to reduce the circuit impedance.
4. Make sure that the PCB GND traces are thick and wide as possible. GND voltage level fluctuation created by high ground current at the time of switching may cause instability of the IC.
5. The internal driver transistors bring on heat because of the I_{IN} current and ON resistance of the driver transistors.

< Example of pattern layout >

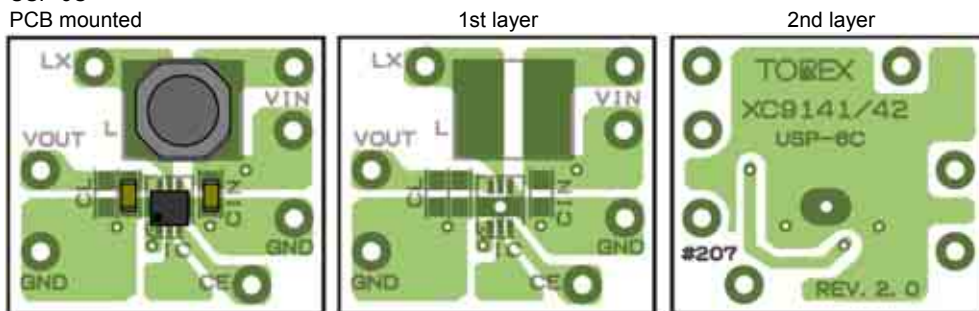
SOT-25

PCB mounted



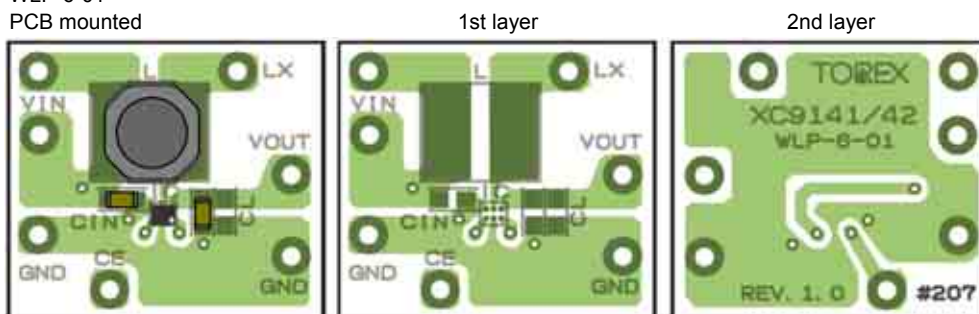
USP-6C

PCB mounted



WLP-6-01

PCB mounted



6. Note on mounting (WLP-6-01)

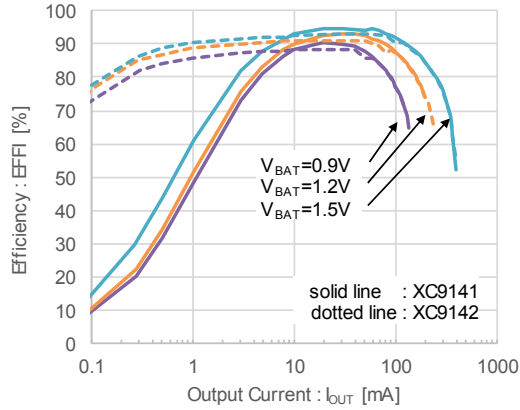
- 6-1. Mount pad design should be optimized for user's conditions.
- 6-2. Sn-AG-Cu is used for the package terminals. If eutectic solder is used, mounting reliability is decreased. Please do not use eutectic solder paste.
- 6-3. When underfill agent is used to increase interfacial bonding strength, please take enough evaluation for selection. Some underfill materials and applied conditions may decrease bonding reliability.
- 6-4. The IC has exposed surface of silicon material in the top marking face and sides so that it is weak against mechanical damages. Please take care of handling to avoid cracks and breaks.
- 6-5. The IC has exposed surface of silicon material in the top marking face and sides. Please use the IC with keeping the circuit open (avoiding short-circuit from the out).
- 6-6. Semi-transparent resin is coated on the circuit face of the package. Please be noted that the usage under strong lights may affects device performance.

TYPICAL PERFORMANCE CHARACTERISTICS

(1) Efficiency vs. Output Current

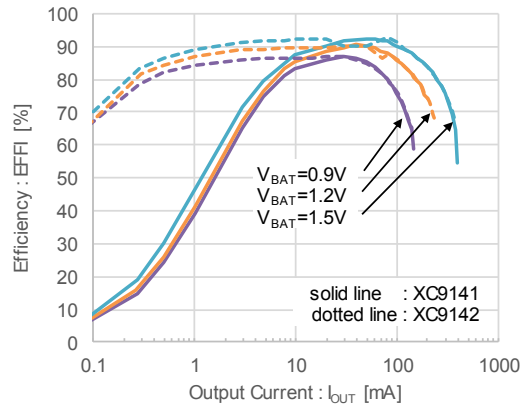
XC9141x18C / XC9142x18C

$L=4.7\mu\text{H}$ (LQH5BPN4R7NT0L)
 $C_{IN}=10\mu\text{F}$ (GRM188R60J106M), $C_L=10\mu\text{F}$ (GRM188R60J106M)



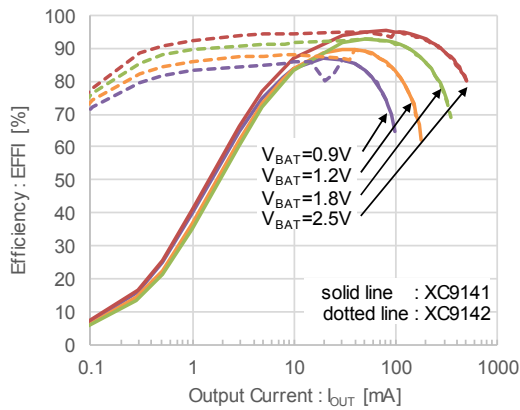
XC9141x18D / XC9142x18D

$L=2.2\mu\text{H}$ (LQH5BPN2R2NT0L)
 $C_{IN}=10\mu\text{F}$ (GRM188R60J106M), $C_L=10\mu\text{F}$ (GRM188R60J106M)



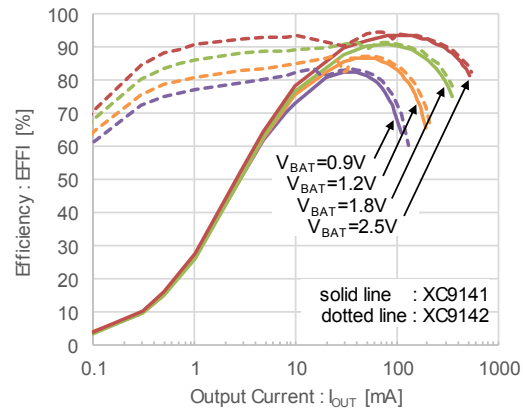
XC9141x33C / XC9142x33C

$L=4.7\mu\text{H}$ (LQH5BPN4R7NT0L)
 $C_{IN}=10\mu\text{F}$ (GRM188R60J106M), $C_L=10\mu\text{F}$ (GRM188R60J106M)



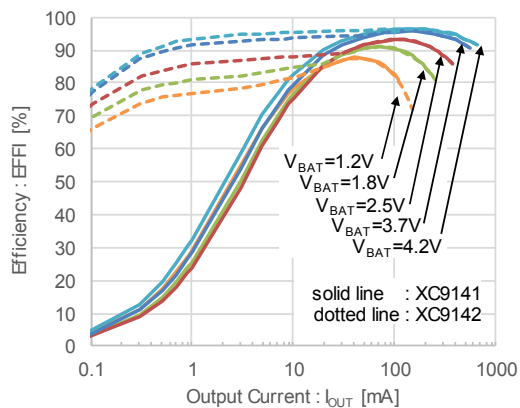
XC9141x33D / XC9142x33D

$L=2.2\mu\text{H}$ (LTF5022T2R2)
 $C_{IN}=10\mu\text{F}$ (GRM188R60J106M), $C_L=10\mu\text{F}$ (GRM188R60J106M)



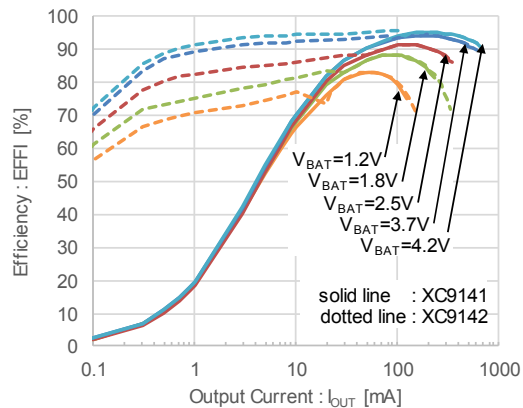
XC9141x50C / XC9142x50C

$L=4.7\mu\text{H}$ (LTF5022T4R7)
 $C_{IN}=10\mu\text{F}$ (GRM188R60J106M), $C_L=20\mu\text{F}$ (GRM188R60J106M x 2)



XC9141x50D / XC9142x50D

$L=2.2\mu\text{H}$ (LTF5022T2R2)
 $C_{IN}=10\mu\text{F}$ (GRM188R60J106M), $C_L=20\mu\text{F}$ (GRM188R60J106M x 2)



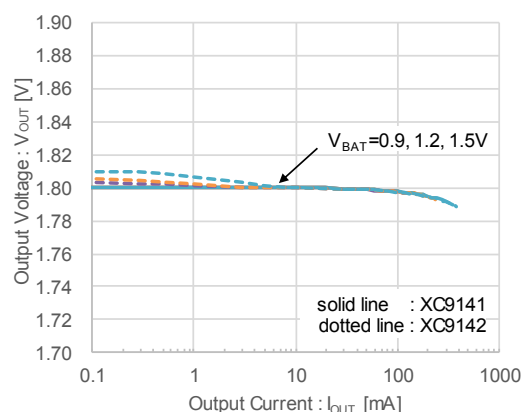
TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(2) Output Voltage vs. Output Current

XC9141x18C / XC9142x18C

L=4.7μH(LQH5BPN4R7NT0L)

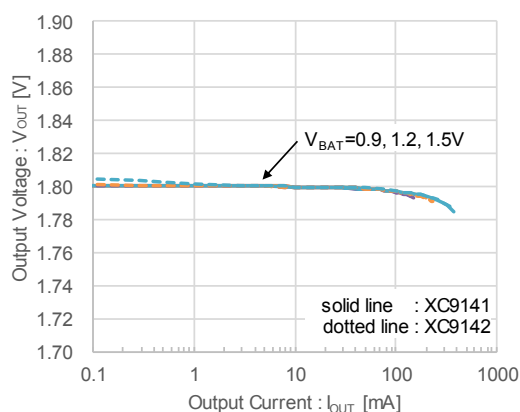
C_{IN}=10μF(GRM188R60J106M), C_L=10μF(GRM188R60J106M)



XC9141x18D / XC9142x18D

L=2.2μH(LQH5BPN2R2NT0L)

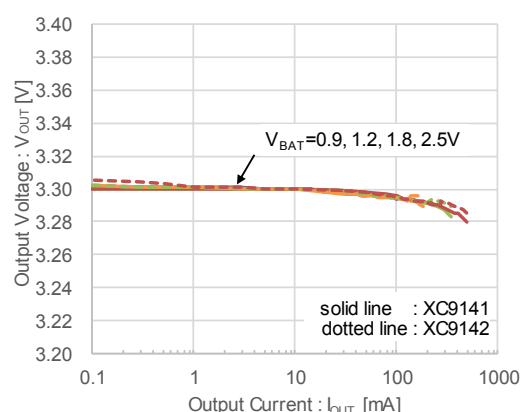
C_{IN}=10μF(GRM188R60J106M), C_L=10μF(GRM188R60J106M)



XC9141x33C / XC9142x33C

L=4.7μH(LQH5BPN4R7NT0L)

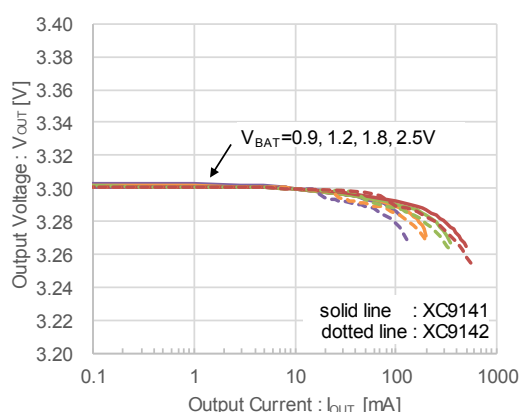
C_{IN}=10μF(GRM188R60J106M), C_L=10μF(GRM188R60J106M)



XC9141x33D / XC9142x33D

L=2.2μH(LTF5022T2R2)

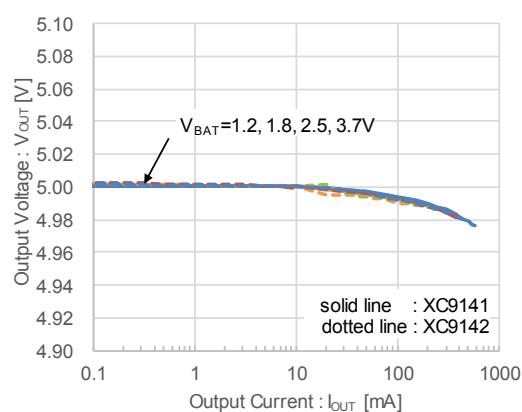
C_{IN}=10μF(GRM188R60J106M), C_L=10μF(GRM188R60J106M)



XC9141x50C / XC9142x50C

L=4.7μH(LTF5022T4R7)

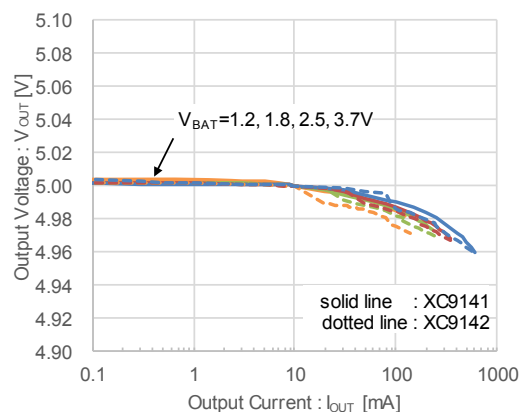
C_{IN}=10μF(GRM188R60J106M), C_L=20μF(GRM188R60J106M x 2)



XC9141x50D / XC9142x50D

L=2.2μH(LTF5022T2R2)

C_{IN}=10μF(GRM188R60J106M), C_L=20μF(GRM188R60J106M x 2)



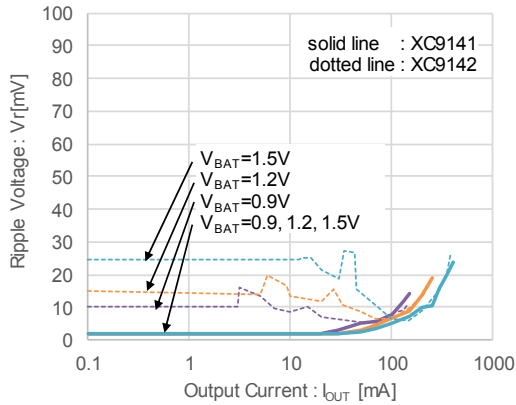
TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(3) Ripple Voltage vs. Output Current

XC9141x18C / XC9142x18C

L=4.7 μ H(LQH5BPN4R7NT0L)

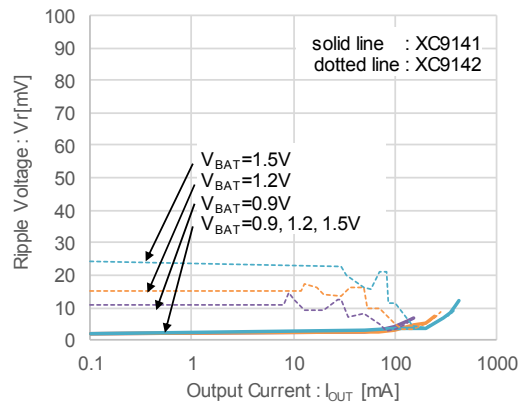
C_{IN}=10 μ F(GRM188R60J106M), C_L=10 μ F(GRM188R60J106M)



XC9141x18D / XC9142x18D

L=2.2 μ H(LQH5BPN2R2NT0L)

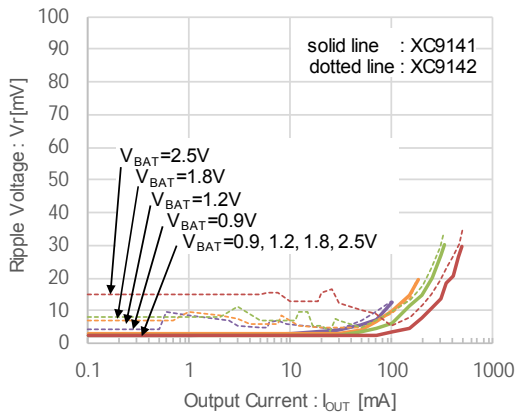
C_{IN}=10 μ F(GRM188R60J106M), C_L=10 μ F(GRM188R60J106M)



XC9141x33C / XC9142x33C

L=4.7 μ H(LQH5BPN4R7NT0L)

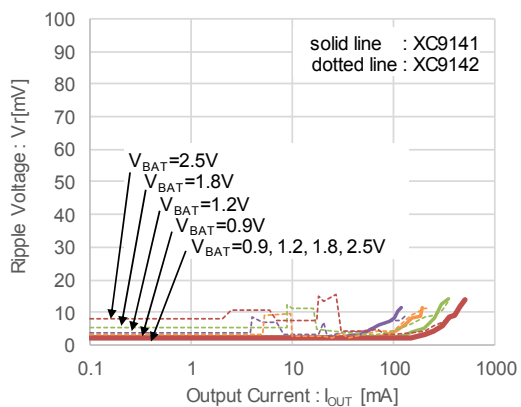
C_{IN}=10 μ F(GRM188R60J106M), C_L=10 μ F(GRM188R60J106M)



XC9141x33D / XC9142x33D

L=2.2 μ H(LTF5022T2R2)

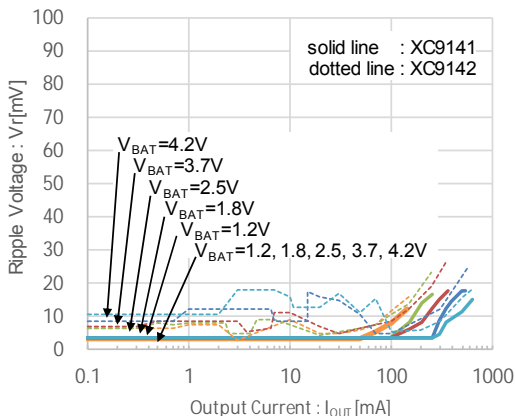
C_{IN}=10 μ F(GRM188R60J106M), C_L=10 μ F(GRM188R60J106M)



XC9141x50C / XC9142x50C

L=4.7 μ H(LTF5022T4R7)

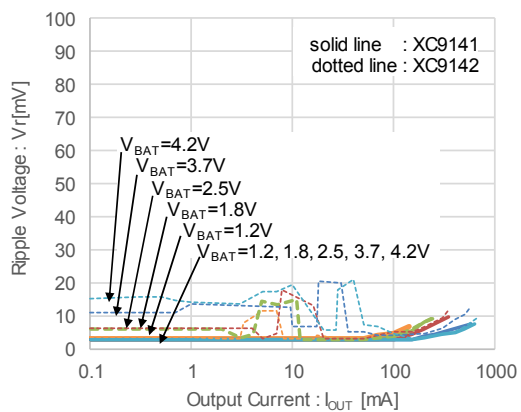
C_{IN}=10 μ F(GRM188R60J106M), C_L=20 μ F(GRM188R60J106M x 2)



XC9141x50D / XC9142x50D

L=2.2 μ H(LTF5022T2R2)

C_{IN}=10 μ F(GRM188R60J106M), C_L=20 μ F(GRM188R60J106M x 2)



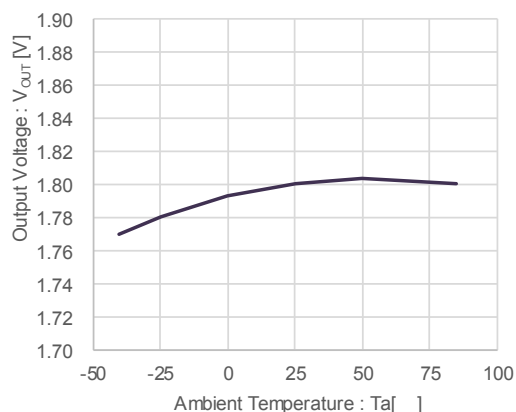
TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(4) Output Voltage vs. Ambient Temperature

XC9141x18C/XC9142x18C

$L=4.7\mu\text{H}$ (LQH5BPN4R7NT0L)

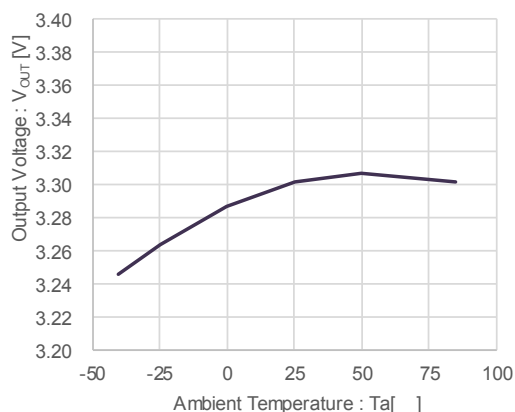
$C_{IN}=10\mu\text{F}$ (GRM188R60J106M), $C_L=10\mu\text{F}$ (GRM188R60J106M)



XC9141x33C/XC9142x33C

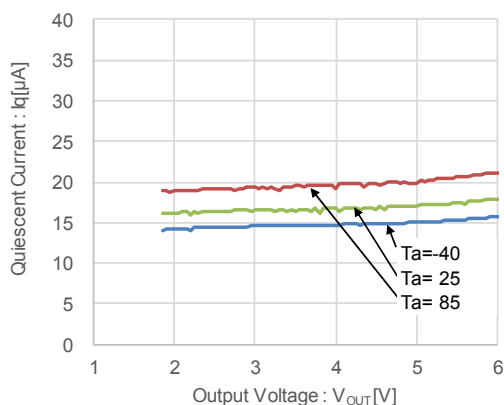
$L=4.7\mu\text{H}$ (LQH5BPN4R7NT0L)

$C_{IN}=10\mu\text{F}$ (GRM188R60J106M), $C_L=10\mu\text{F}$ (GRM188R60J106M)

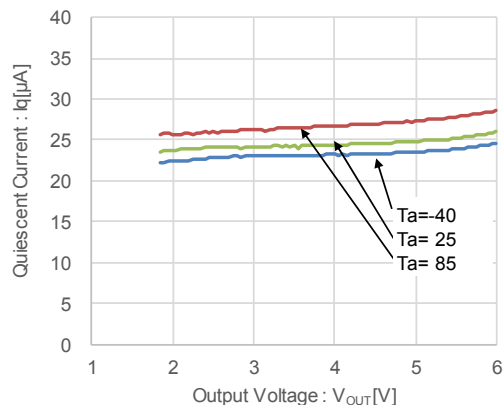


(5) Quiescent Current vs. Output Voltage

XC9142x18C

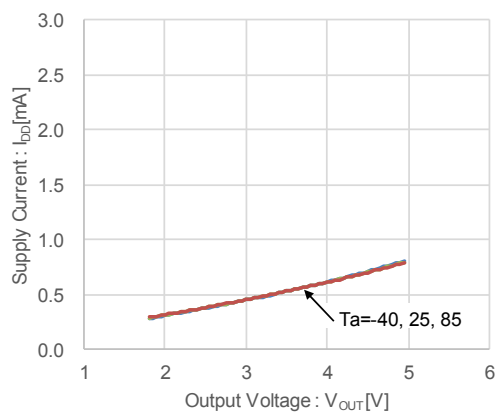


XC9142x18D

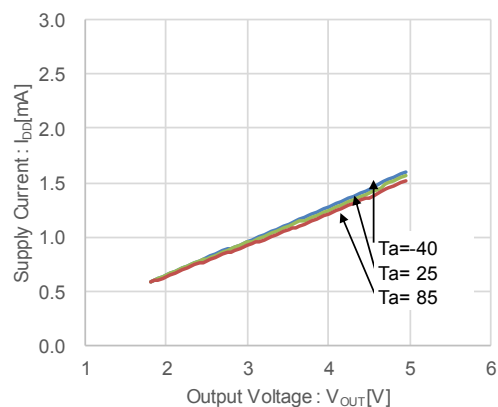


(6) Supply Current vs. Output voltage

XC9141x50C / XC9142x50C

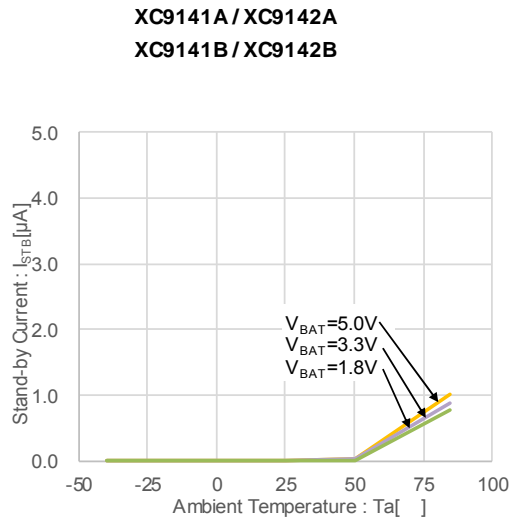


XC9141x50D / XC9142x50D

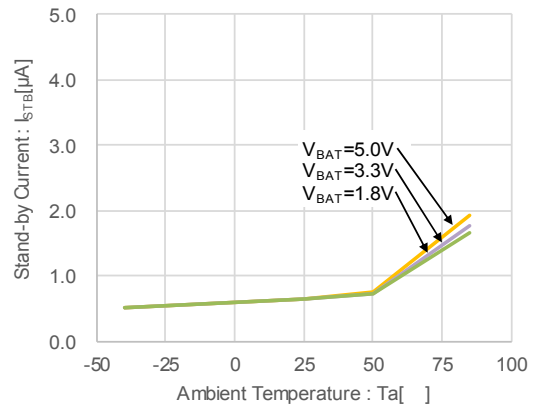


TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

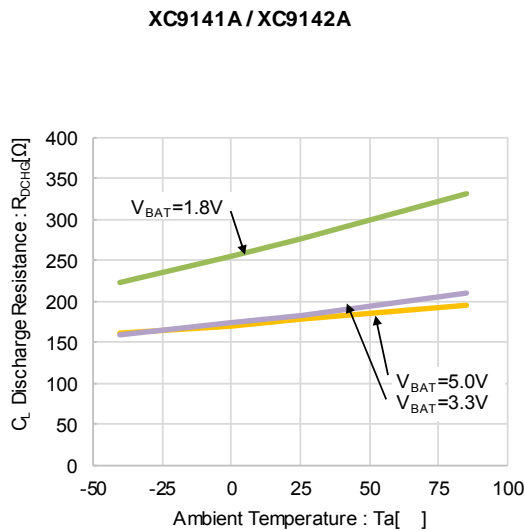
(7) Stand-by Current vs. Ambient Temperature



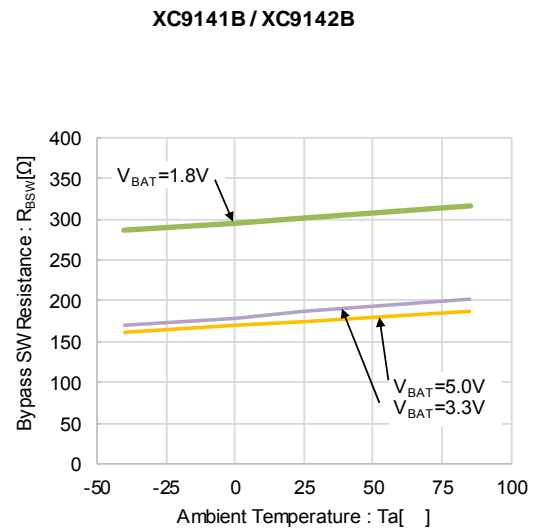
XC9142C



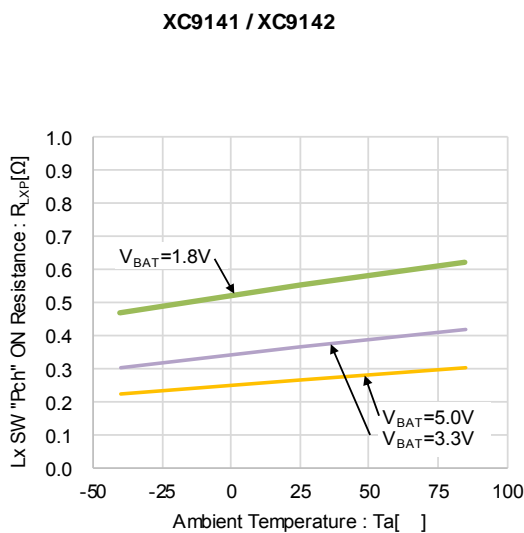
(8) C_L Discharge Resistance vs. Ambient Temperature



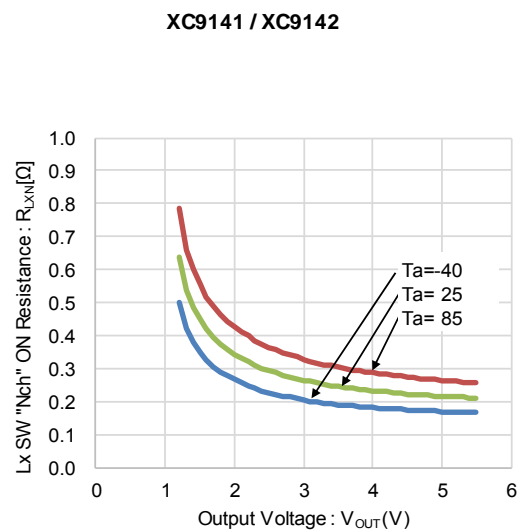
(9) Bypass SW Resistance vs. Ambient Temperature



(10) Lx SW "Pch" ON Resistance vs. Ambient Temperature

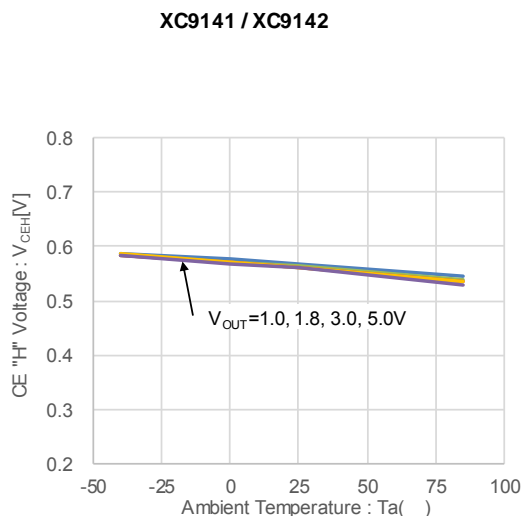


(11) Lx SW "Nch" ON Resistance vs. Output Voltage

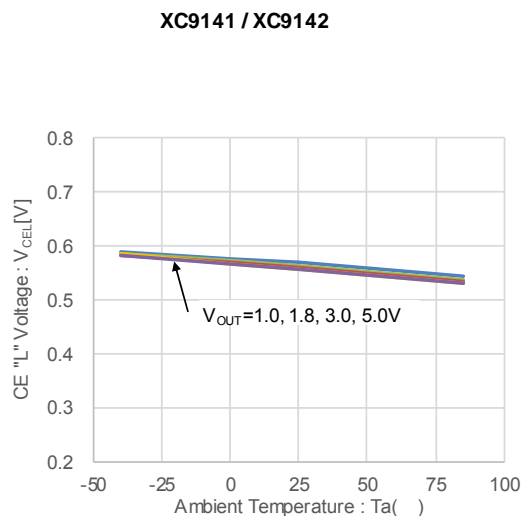


TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

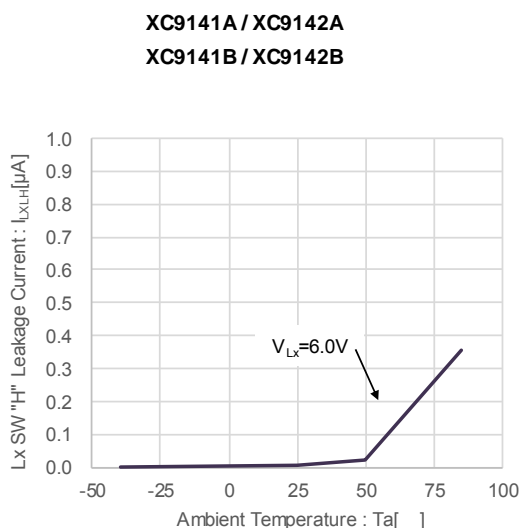
(12) CE "H" Voltage vs. Ambient Temperature



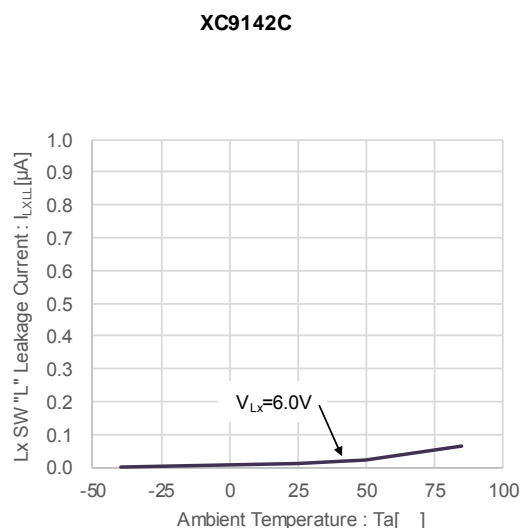
(13) CE "L" Voltage vs. Ambient Temperature



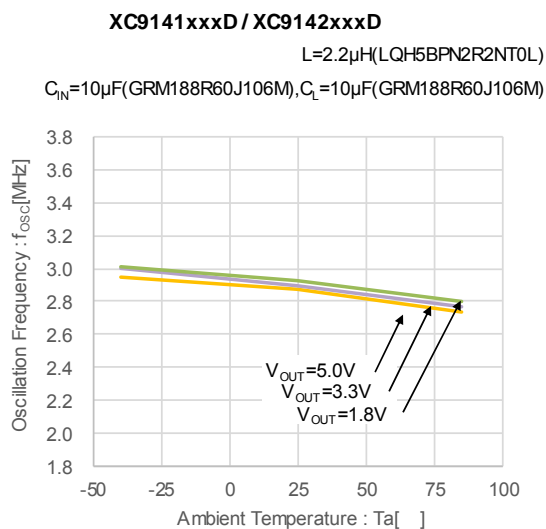
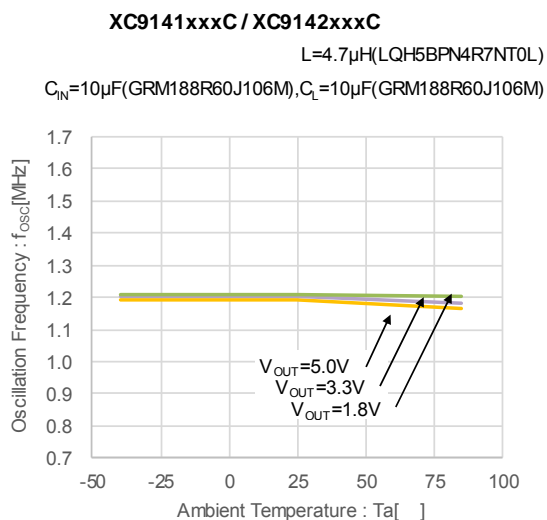
(14) Lx SW "H" Leakage Current vs. Ambient temperature



(15) Lx SW "L" Leakage Current vs. Ambient temperature



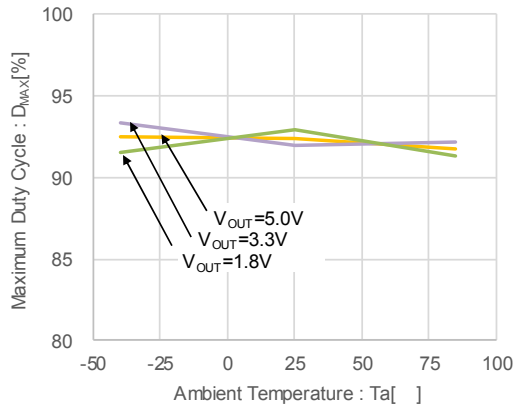
(16) Oscillation Frequency vs. Ambient temperature



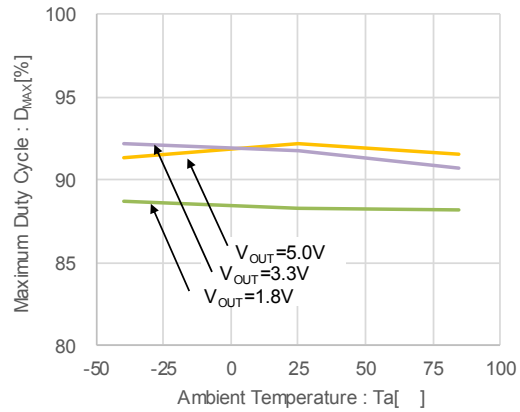
TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(17) Maximum Duty Cycle vs. Ambient temperature

XC9141xxxC / XC9142xxxC

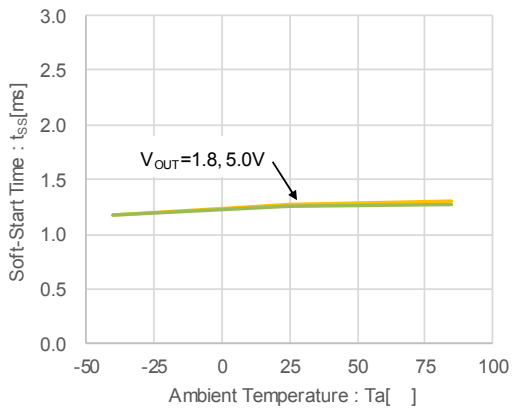


XC9141xxxD / XC9142xxxD

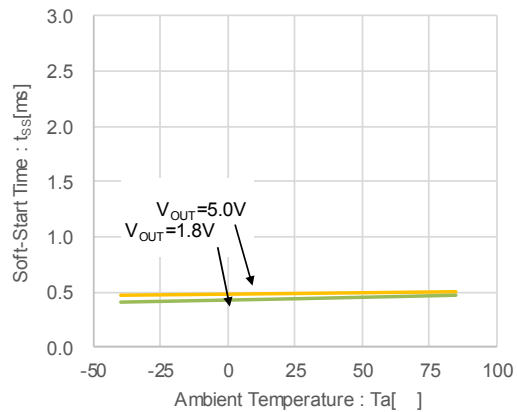


(18) Soft-Start Time vs. Ambient temperature

XC9141xxxC / XC9142xxxC



XC9141xxxD / XC9142xxxD

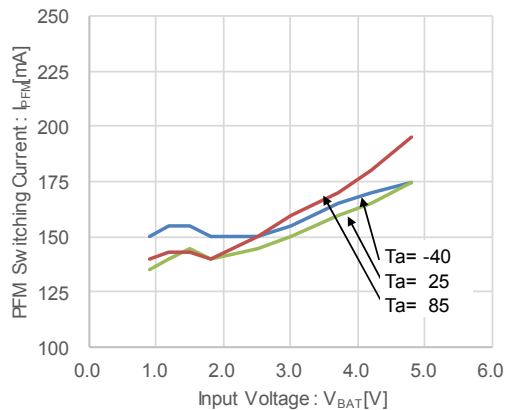


(19) PFM Switching Current vs. Input Voltage

XC9142x50C

$L=4.7\mu\text{H}$ (LQH5BPN4R7NT0L)

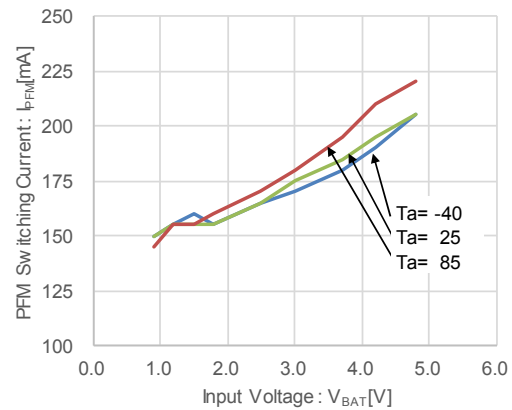
$C_{IN}=10\mu\text{F}$ (GRM188R60J106M), $C_L=10\mu\text{F}$ (GRM188R60J106M)



XC9142x50D

$L=2.2\mu\text{H}$ (LQH5BPN2R2NT0L)

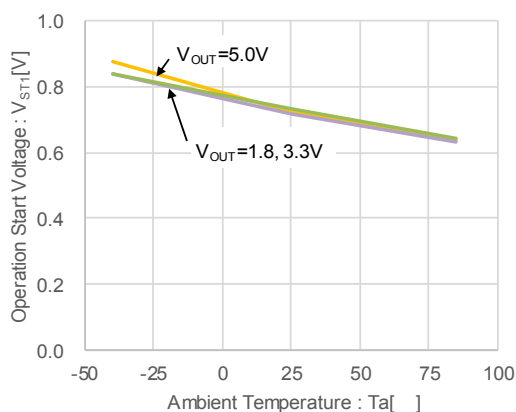
$C_{IN}=10\mu\text{F}$ (GRM188R60J106M), $C_L=10\mu\text{F}$ (GRM188R60J106M)



TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

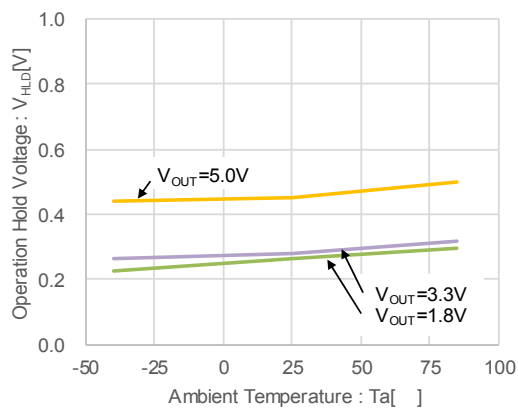
(20) Operation Start Voltage vs. Ambient temperature

XC9141 / XC9142



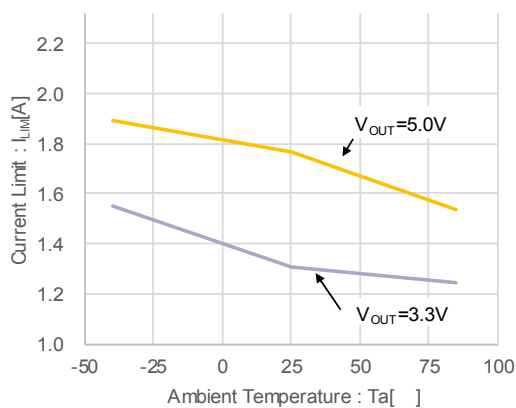
(21) Operation Hold Voltage vs. Ambient temperature

XC9141 / XC9142

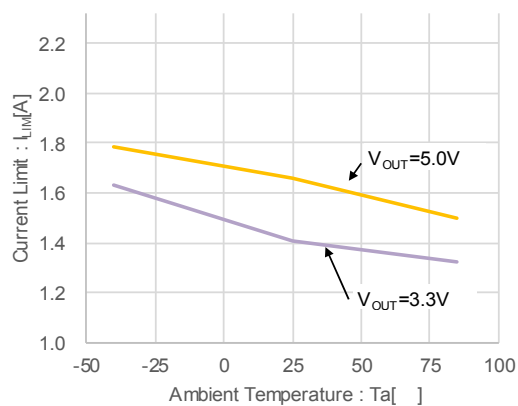


(22) Current Limit vs. Ambient temperature

XC9141xxxC / XC9142xxxC



XC9141xxxD / XC9142xxxD



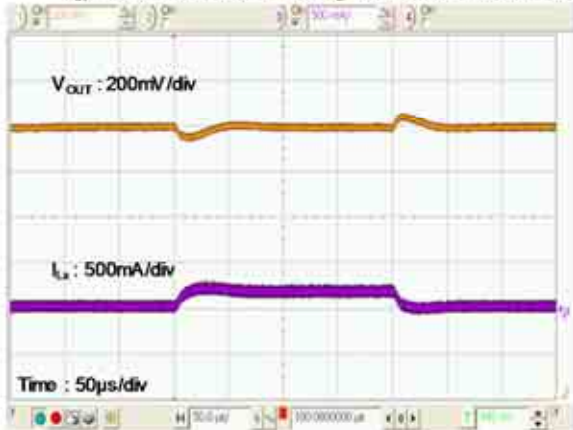
TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(23) Load Transient Response

XC9141x18C

$V_{BAT}=1.2V, V_{OUT}=1.8V, I_{OUT}=10mA \leftrightarrow 100mA$
 $L=4.7\mu H(LTF5022T4R7)$

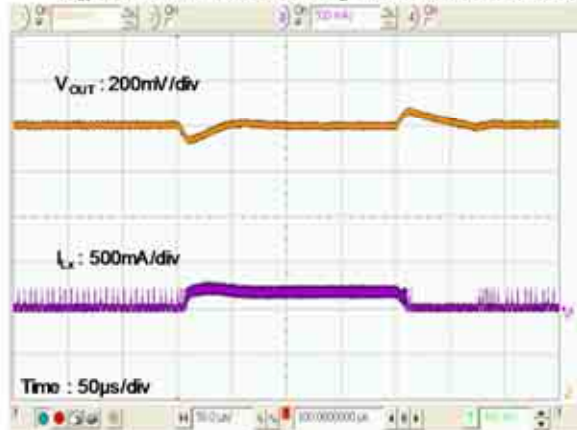
$C_{IN}=10\mu F(GRM188R60J106M), C_L=10\mu F(GRM188R60J106M)$



XC9142x18C

$V_{BAT}=1.2V, V_{OUT}=1.8V, I_{OUT}=10mA \leftrightarrow 100mA$
 $L=4.7\mu H(LTF5022T4R7)$

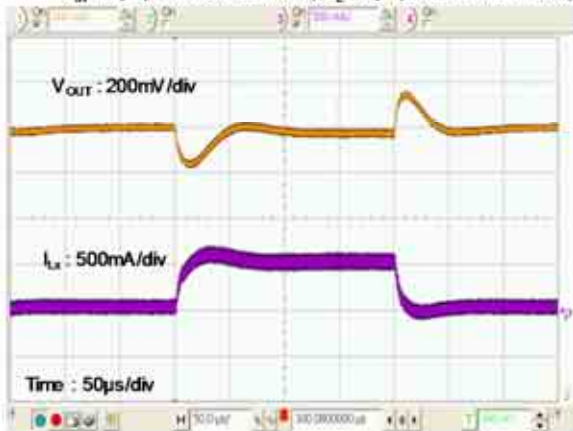
$C_{IN}=10\mu F(GRM188R60J106M), C_L=10\mu F(GRM188R60J106M)$



XC9141x33C

$V_{BAT}=2.4V, V_{OUT}=3.3V, I_{OUT}=20mA \leftrightarrow 300mA$
 $L=4.7\mu H(LTF5022T4R7)$

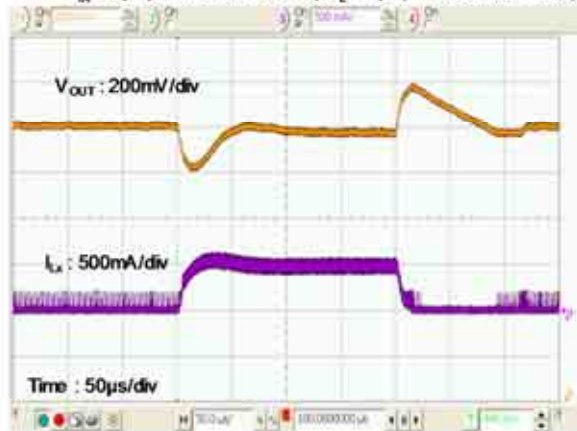
$C_{IN}=10\mu F(GRM188R60J106M), C_L=10\mu F(GRM188R60J106M)$



XC9142x33C

$V_{BAT}=2.4V, V_{OUT}=3.3V, I_{OUT}=20mA \leftrightarrow 300mA$
 $L=4.7\mu H(LTF5022T4R7)$

$C_{IN}=10\mu F(GRM188R60J106M), C_L=10\mu F(GRM188R60J106M)$



XC9141x50C

$V_{BAT}=3.7V, V_{OUT}=5.0V, I_{OUT}=20mA \leftrightarrow 300mA$
 $L=4.7\mu H(LTF5022T4R7)$

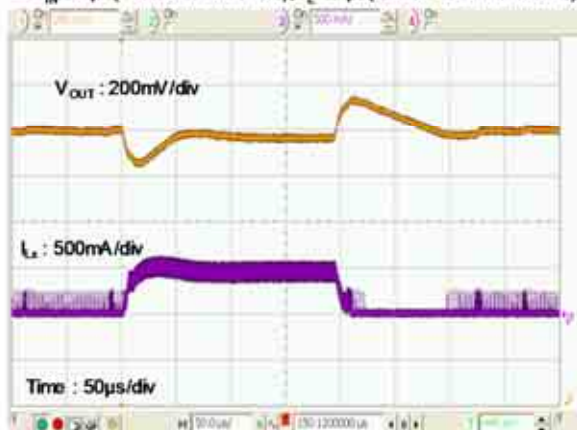
$C_{IN}=10\mu F(GRM188R60J106M), C_L=20\mu F(GRM188R60J106M \times 2)$



XC9142x50C

$V_{BAT}=3.7V, V_{OUT}=5.0V, I_{OUT}=20mA \leftrightarrow 300mA$
 $L=4.7\mu H(LTF5022T4R7)$

$C_{IN}=10\mu F(GRM188R60J106M), C_L=20\mu F(GRM188R60J106M \times 2)$



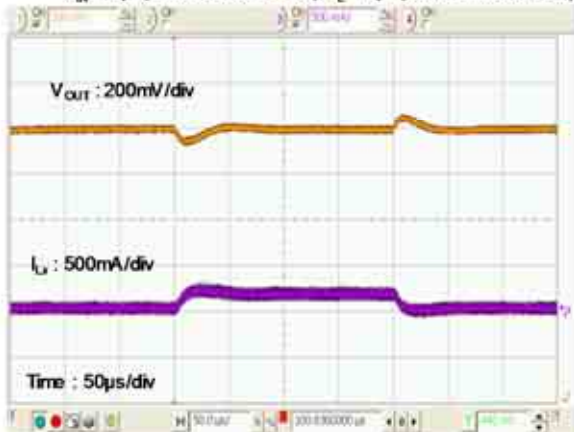
TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

(23) Load Transient Response

XC9141x18D

$V_{BAT}=1.2V, V_{OUT}=1.8V, I_{OUT}=10mA \leftrightarrow 100mA$
 $L=2.2\mu H(LTF5022T2R2)$

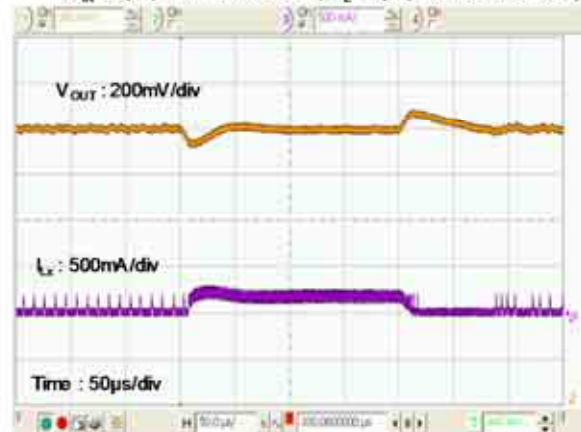
$C_{IN}=10\mu F(GRM188R60J106M), C_L=10\mu F(GRM188R60J106M)$



XC9142x18D

$V_{BAT}=1.2V, V_{OUT}=1.8V, I_{OUT}=10mA \leftrightarrow 100mA$
 $L=2.2\mu H(LTF5022T2R2)$

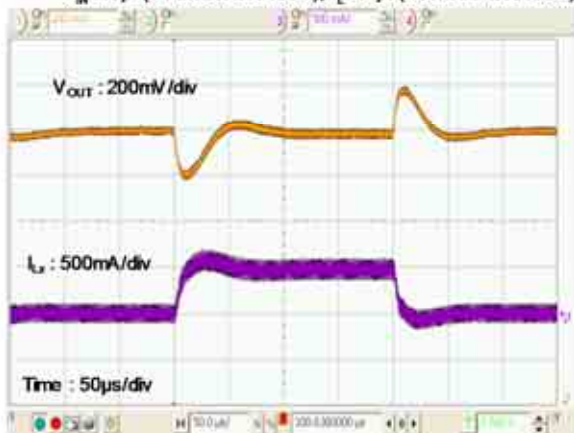
$C_{IN}=10\mu F(GRM188R60J106M), C_L=10\mu F(GRM188R60J106M)$



XC9141x33D

$V_{BAT}=2.4V, V_{OUT}=3.3V, I_{OUT}=20mA \leftrightarrow 300mA$
 $L=2.2\mu H(LTF5022T2R2)$

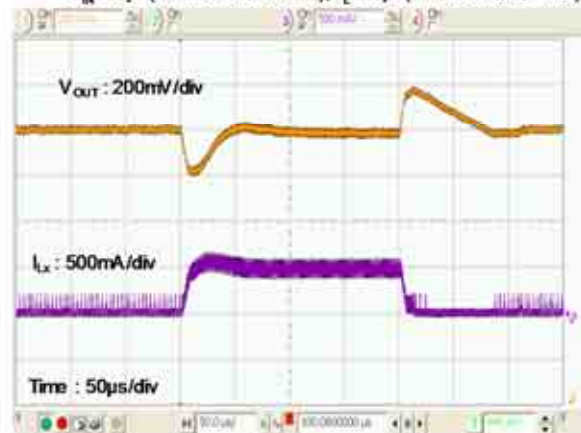
$C_{IN}=10\mu F(GRM188R60J106M), C_L=10\mu F(GRM188R60J106M)$



XC9142x33D

$V_{BAT}=2.4V, V_{OUT}=3.3V, I_{OUT}=20mA \leftrightarrow 300mA$
 $L=2.2\mu H(LTF5022T2R2)$

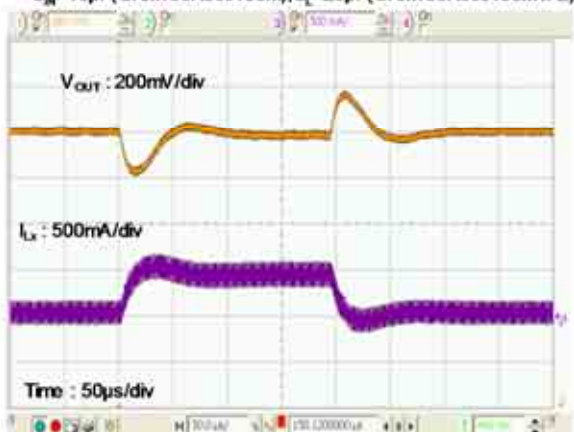
$C_{IN}=10\mu F(GRM188R60J106M), C_L=10\mu F(GRM188R60J106M)$



XC9141x50D

$V_{BAT}=3.7V, V_{OUT}=5.0V, I_{OUT}=20mA \leftrightarrow 300mA$
 $L=2.2\mu H(LTF5022T2R2)$

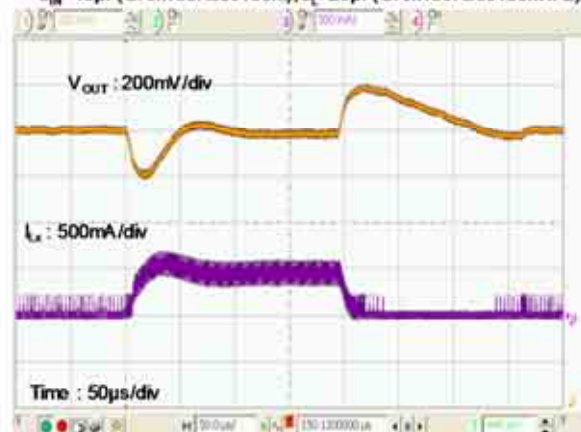
$C_{IN}=10\mu F(GRM188R60J106M), C_L=20\mu F(GRM188R60J106M \times 2)$



XC9142x50D

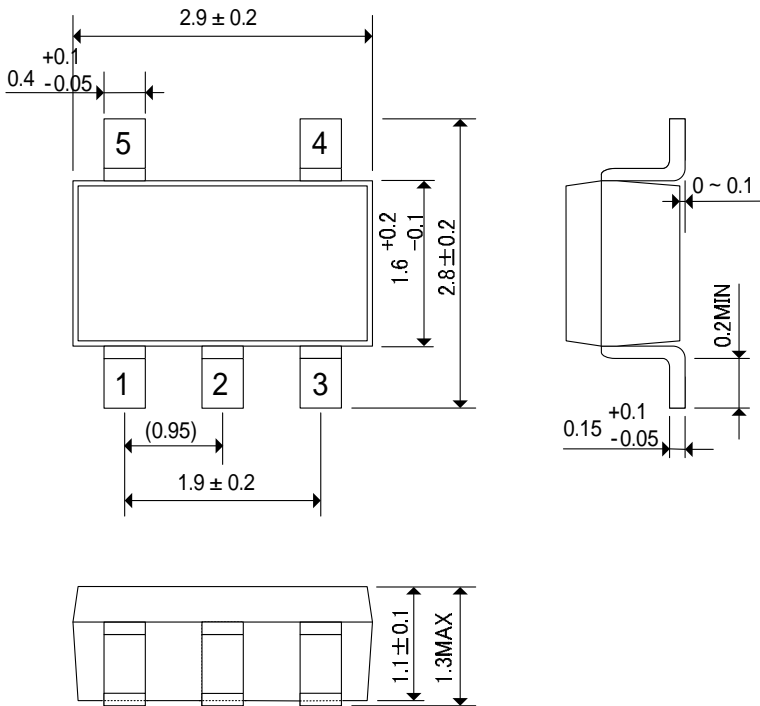
$V_{BAT}=3.7V, V_{OUT}=5.0V, I_{OUT}=20mA \leftrightarrow 300mA$
 $L=2.2\mu H(LTF5022T2R2)$

$C_{IN}=10\mu F(GRM188R60J106M), C_L=20\mu F(GRM188R60J106M \times 2)$

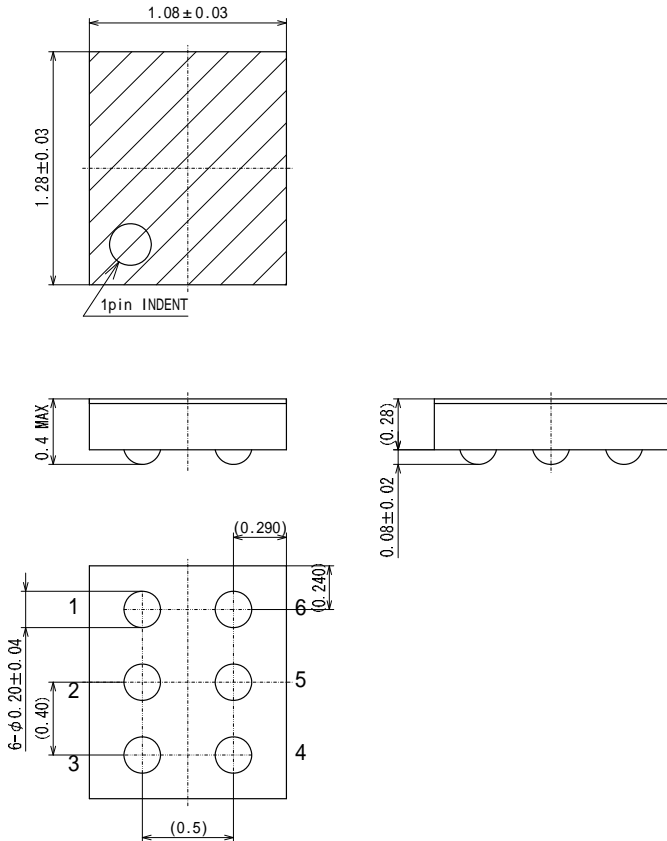


PACKAGING INFORMATION

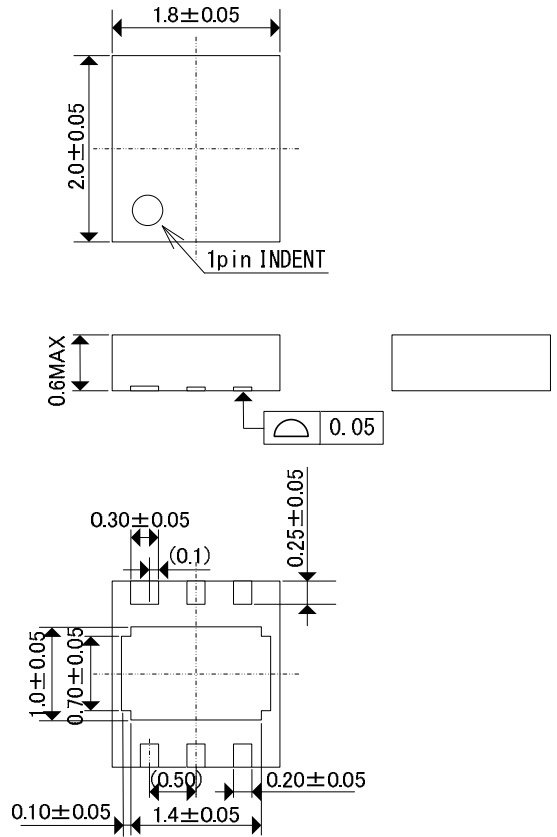
SOT-25 (unit: mm)



WLP-6-01 (unit: mm)

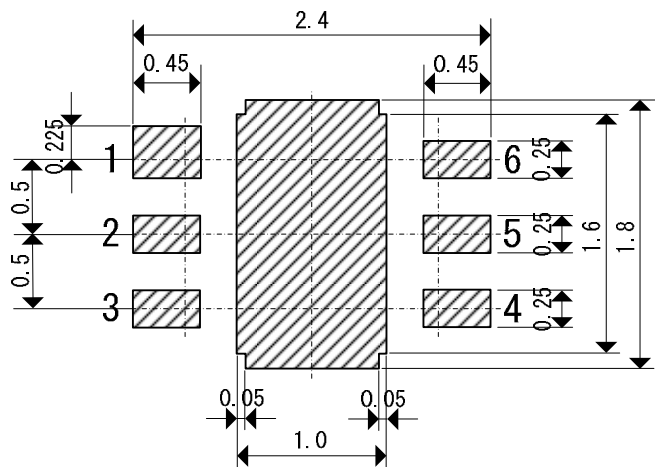


USP-6C (unit: mm)

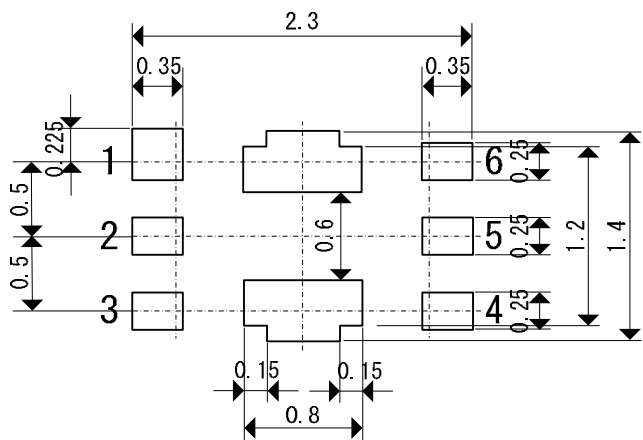


PACKAGING INFORMATION (Continued)

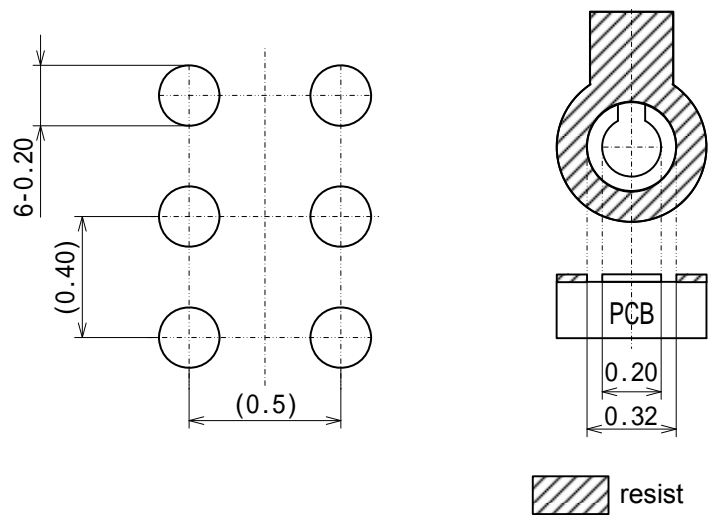
USP-6C Reference Pattern Layout (unit: mm)



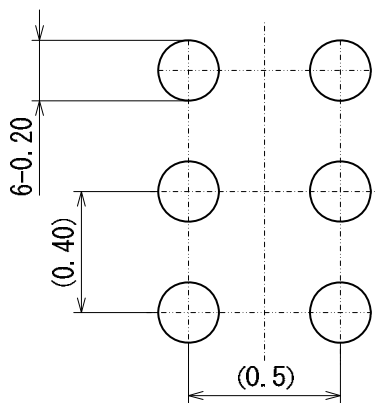
USP-6C Reference Metal Mask Design (unit: mm)



WLP-6-01 Reference Pattern Layout / Reference Pattern Layout detail (unit: mm)



WLP-6-01 Reference Metal Mask Design (unit: mm)



SOT-25 Power Dissipation

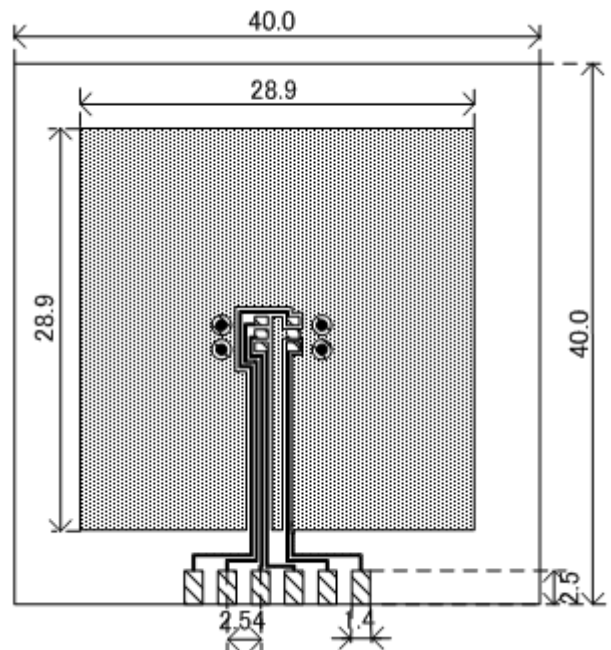
Power dissipation data for the SOT-25 is shown in this page.

The value of power dissipation varies with the mount board conditions.

Please use this data as one of reference data taken in the described condition.

1. Measurement Condition (Reference data)

- Condition: Mount on a board
- Ambient: Natural convection
- Soldering: Lead (Pb) free
- Board: Dimensions 40 x 40 mm (1600 mm² in one side)
Copper (Cu) traces occupy 50% of the board area in top and back faces
Package heat-sink is tied to the copper traces
(Board of SOT-26 is used.)
- Material: Glass Epoxy (FR-4)
- Thickness: 1.6 mm
- Through-hole: 4 x 0.8 Diameter

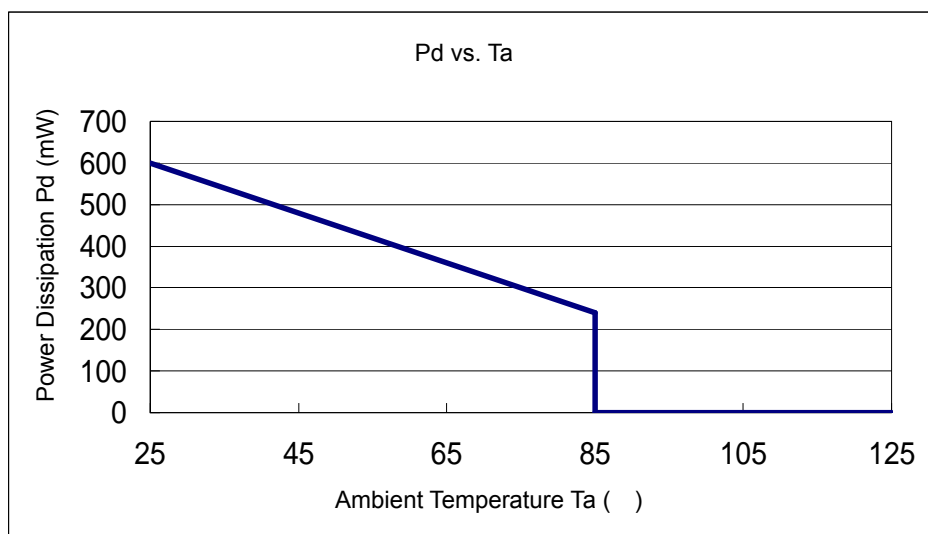


Evaluation Board (Unit: mm)

2. Power Dissipation vs. Ambient temperature

Board Mount (T_j max = 125 °C)

Ambient Temperature (°C)	Power Dissipation Pd (mW)	Thermal Resistance (°C/W)
25	600	166.67
85	240	



USP-6C Power Dissipation

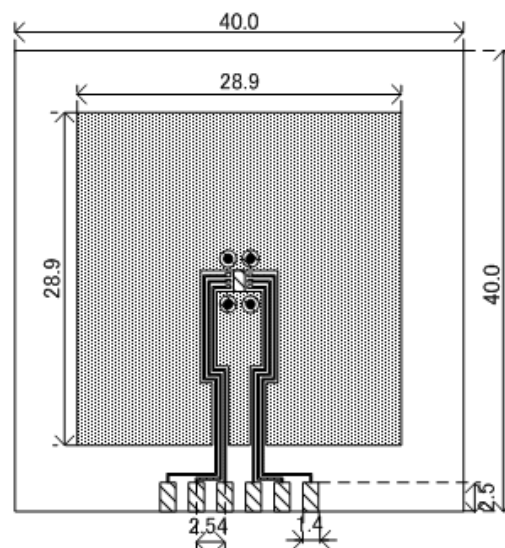
Power dissipation data for the USP-6C is shown in this page.

The value of power dissipation varies with the mount board conditions.

Please use this data as one of reference data taken in the described condition.

1. Measurement Condition (Reference data)

Condition: Mount on a board
 Ambient: Natural convection
 Soldering: Lead (Pb) free
 Board: Dimensions 40mm×40mm (1600mm² in one side)
 Copper (Cu) traces occupy 50% of the board area
 in top and back faces
 Package heat-sink is tied to the copper traces
 Material: Glass Epoxy (FR-4)
 Thickness: 1.6mm
 Through-hole: 4 x 0.8 Diameter

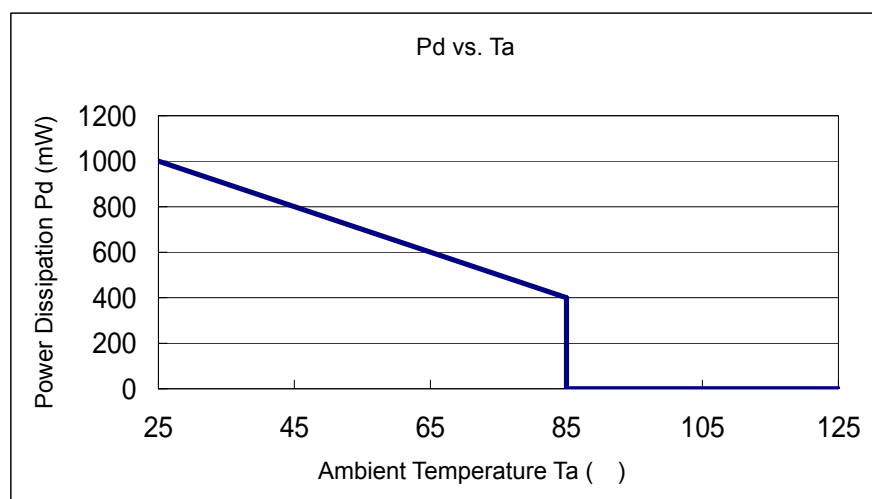


Evaluation Board (Unit: mm)

2. Power Dissipation vs. Ambient temperature

Board Mount (T_j max=125 °C)

Ambient Temperature (°C)	Power Dissipation Pd (mW)	Thermal Resistance (°C/W)
25	1000	100.00
85	400	



WLP-6-01 Power Dissipation

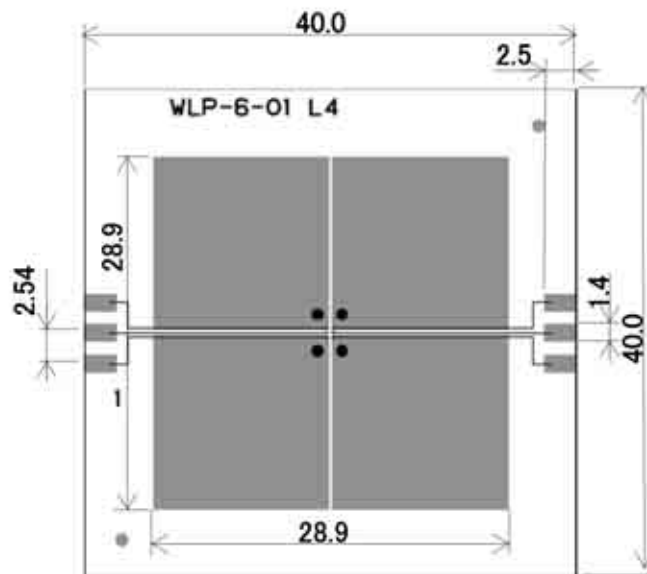
Power dissipation data for the WLP-6-01 is shown in this page.

The value of power dissipation varies with the mount board conditions.

Please use this data as one of reference data taken in the described condition.

1. Measurement Condition (Reference data)

Condition:	Mount on a board
Ambient:	Natural convection
Soldering:	Lead (Pb) free
Board:	40mm×40mm (1600mm ² in one side)
Metal Area:	1st Metal Layer about 50%
	2nd Inner Metal Layer about 50%
	3rd Inner Metal Layer about 50%
	4th Metal Layer about 50%
Material:	Glass Epoxy (FR-4)
Thickness:	1.6mm
Through-hole:	4 x 0.8 Diameter

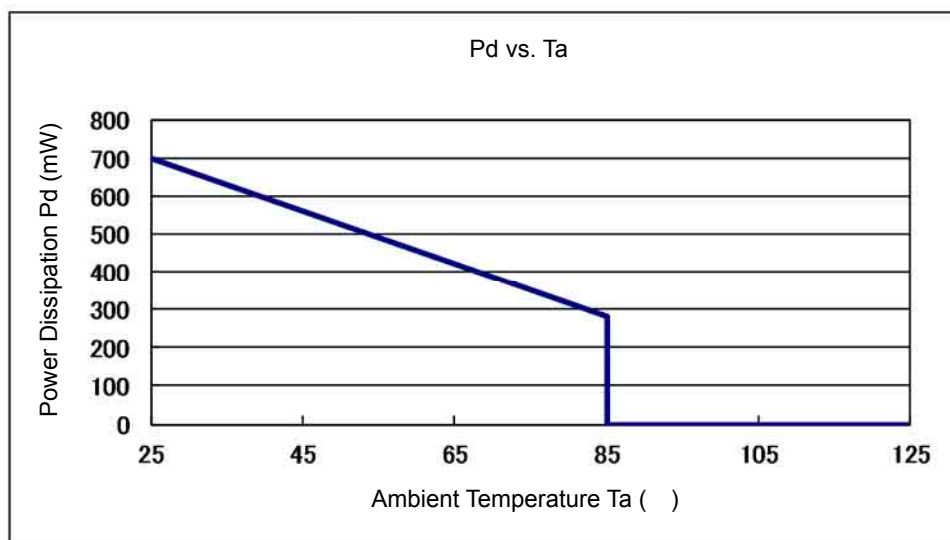


Evaluation Board (Unit: mm)

2. Power Dissipation vs. Ambient temperature

Board Mount ($T_J \text{ max}=125$)

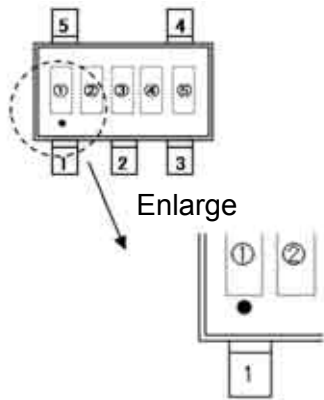
Ambient Temperature ()	Power Dissipation Pd (mW)	Thermal Resistance (/W)
25	700	142.86
85	280	



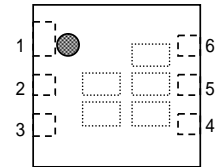
MARKING RULE

SOT-25 (Under dot)

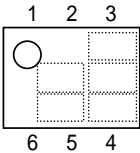
(*) SOT-25 has a dot mark, which is printed under MARK (refer to drawings below).



USP-6C



WLP-6-01



represents products series

MARK	PRODUCT SERIES
Y	XC9141/42xxxxxx

represents products series, Oscillation Frequency, and output voltage range

SERIES	OSCILLATION FREQUENCY	OUTPUT VOLTAGE RANGE [V]		PRODUCT SERIES
		1.8 ~ 3.7	3.8 ~ 5.5	
XC9141A	1.2MHz	0	1	XC9141AxxCxx-G
XC9141B		2	3	XC9141BxxCxx-G
XC9141A	3.0MHz	4	5	XC9141AxxDxx-G
XC9141B		6	7	XC9141BxxDxx-G
XC9142A	1.2MHz	A	B	XC9142AxxCxx-G
XC9142B		C	D	XC9142BxxCxx-G
XC9142C		E	F	XC9142CxxCxx-G
XC9142A	3.0MHz	H	K	XC9142AxxDxx-G
XC9142B		L	M	XC9142BxxDxx-G
XC9142C		N	P	XC9142CxxDxx-G

represents output voltage

MARK	OUTPUT VOLTAGE [V]		MARK	OUTPUT VOLTAGE [V]	
0	1.8	3.8	A	2.8	4.8
1	1.9	3.9	B	2.9	4.9
2	2.0	4.0	C	3.0	5.0
3	2.1	4.1	D	3.1	5.1
4	2.2	4.2	E	3.2	5.2
5	2.3	4.3	F	3.3	5.3
6	2.4	4.4	H	3.4	5.4
7	2.5	4.5	K	3.5	5.5
8	2.6	4.6	L	3.6	-
9	2.7	4.7	M	3.7	-

represents production lot number

01 ~ 09, 0A ~ 0Z, 11 ~ 9Z, A1 ~ A9, AA ~ AZ, B1 ~ ZZ in order.

(G, I, J, O, Q, W excluded)

* No character inversion used.

1. The product and product specifications contained herein are subject to change without notice to improve performance characteristics. Consult us, or our representatives before use, to confirm that the information in this datasheet is up to date.
2. The information in this datasheet is intended to illustrate the operation and characteristics of our products. We neither make warranties or representations with respect to the accuracy or completeness of the information contained in this datasheet nor grant any license to any intellectual property rights of ours or any third party concerning with the information in this datasheet.
3. Applicable export control laws and regulations should be complied and the procedures required by such laws and regulations should also be followed, when the product or any information contained in this datasheet is exported.
4. The product is neither intended nor warranted for use in equipment of systems which require extremely high levels of quality and/or reliability and/or a malfunction or failure which may cause loss of human life, bodily injury, serious property damage including but not limited to devices or equipment used in 1) nuclear facilities, 2) aerospace industry, 3) medical facilities, 4) automobile industry and other transportation industry and 5) safety devices and safety equipment to control combustions and explosions. Do not use the product for the above use unless agreed by us in writing in advance.
5. Although we make continuous efforts to improve the quality and reliability of our products; nevertheless Semiconductors are likely to fail with a certain probability. So in order to prevent personal injury and/or property damage resulting from such failure, customers are required to incorporate adequate safety measures in their designs, such as system fail safes, redundancy and fire prevention features.
6. Our products are not designed to be Radiation-resistant.
7. Please use the product listed in this datasheet within the specified ranges.
8. We assume no responsibility for damage or loss due to abnormal use.
9. All rights reserved. No part of this datasheet may be copied or reproduced unless agreed by Torex Semiconductor Ltd in writing in advance.

TOREX SEMICONDUCTOR LTD.